



The ALCOR ASIC for the ePIC dRICH

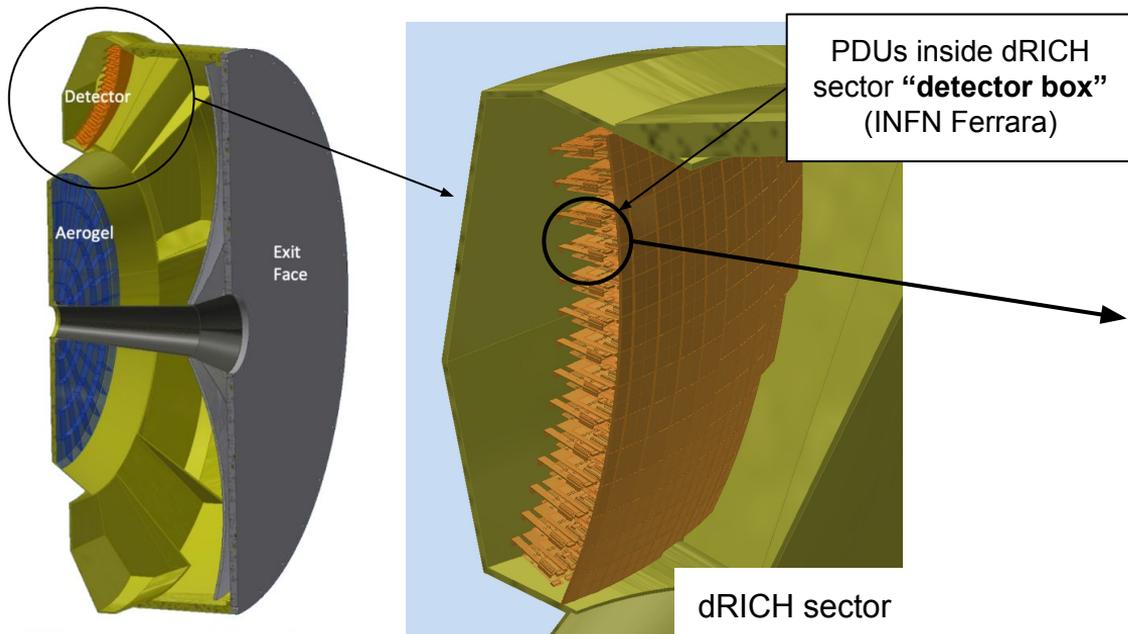
Fabio Cossio (INFN Torino)
on behalf of the ALCOR group

Giornate Nazionali ePIC Italia
Padova, 16-18 June 2025

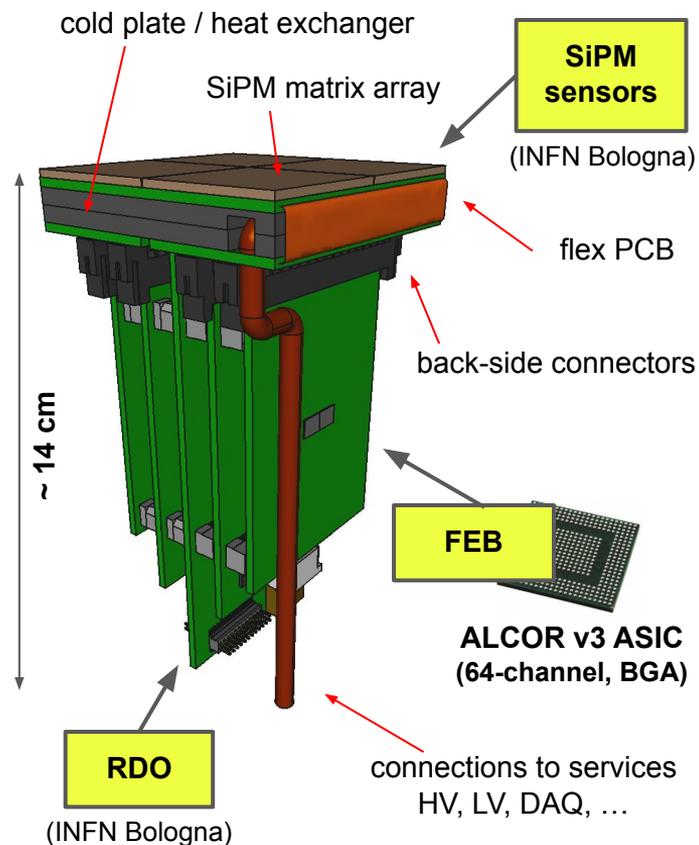
Outline

- ALCOR ASIC requirements and architecture overview
- Main results from ALCOR v2
- ALCOR v3: design upgrades and BGA packaging
- ALCOR FEB
- Towards production and QA/QC
- Conclusions

dRICH electronics



PDU: PhotoDetector Unit



- **1 PDU:** 4x64 SiPM array device (256 channels), **4 FEBs**, **1 RDO**
- **1 ALCOR** (64 channels) per **FEB:** 8x8 SiPM matrix readout
- 6 sectors: 208 PDUs/sector → 1248 PDUs for full dRICH readout
- **4992 FEBs** → **4992 ALCOR v3** (64-channel)
- **319488** readout **channels**

Motivation and status



Main requirements:

- Provide **single-photon time tagging** ($\sigma_t = 150$ ps) of signals coming from SiPM sensors
- Cope with **SiPM DCR: 300 kHz/channel** (at max SiPM radiation damage)

ALCOR v2.0 - v2.1 (ALCOR-32)

- Extensively used within the dRICH Collaboration during 2023-25: lab tests, beam-tests, irradiation tests

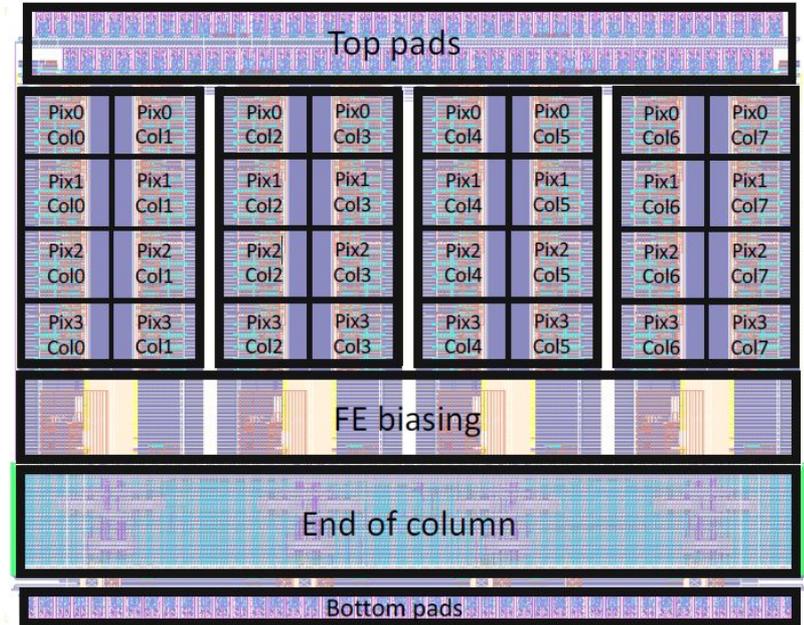
ALCOR v3 (ALCOR-64)

- First version to include all features and specifications required for the ePIC dRICH:
 - 64 channels, BGA package
 - Shutter + other EIC-driven features
- **MPW tapeout on Apr 8th 2025** (delay due to MPW run canceled by UMC: Nov 2024 → Apr 2025)
- Started production of **BGA substrate**
- Now adapting DAQ and test setups for new version, **electrical characterization** expected to start **this Fall**

ALCOR: A Low Power Chip for Optical Sensor Readout

ALCOR-32 (ALCOR v2 - v2.1)

- **32-pixel** matrix (8x4) mixed-signal ASIC ($4.95 \times 3.78 \text{ mm}^2$)
- Single-photon time tagging + **Time-over-Threshold** or **Slew-Rate** measurements for **time walk correction**
- On-chip **signal amplification, conditioning** and **digitization**, 32-bit event word
- Trigger-less readout with fully digital output: **4 LVDS 320 MHz** DDR Tx links
- Power consumption **~10-12 mW/channel**
- **0.11 μm CMOS technology**

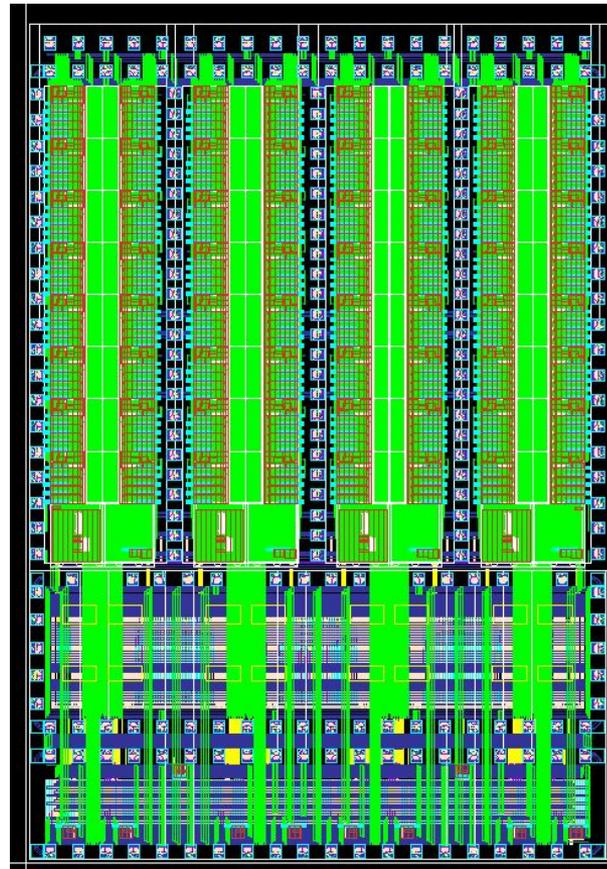


<https://doi.org/10.1016/j.nima.2024.169817>

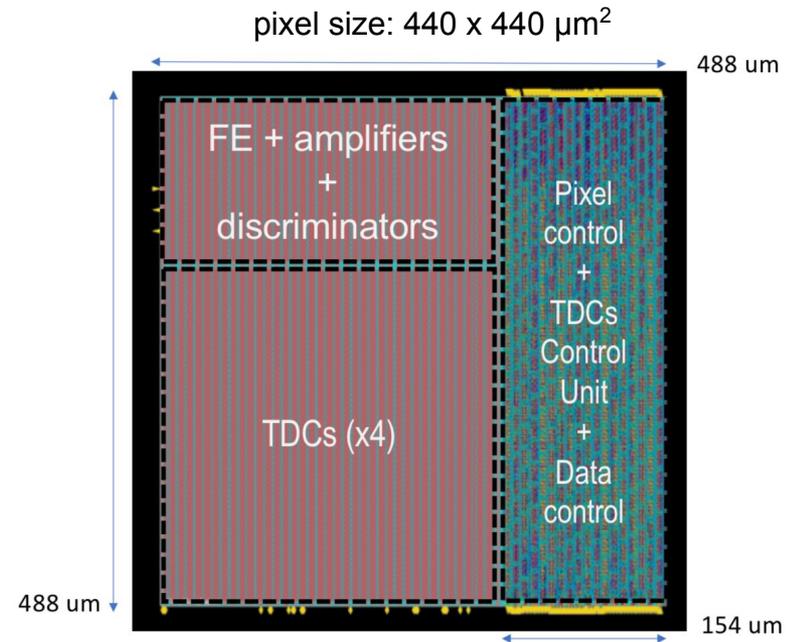
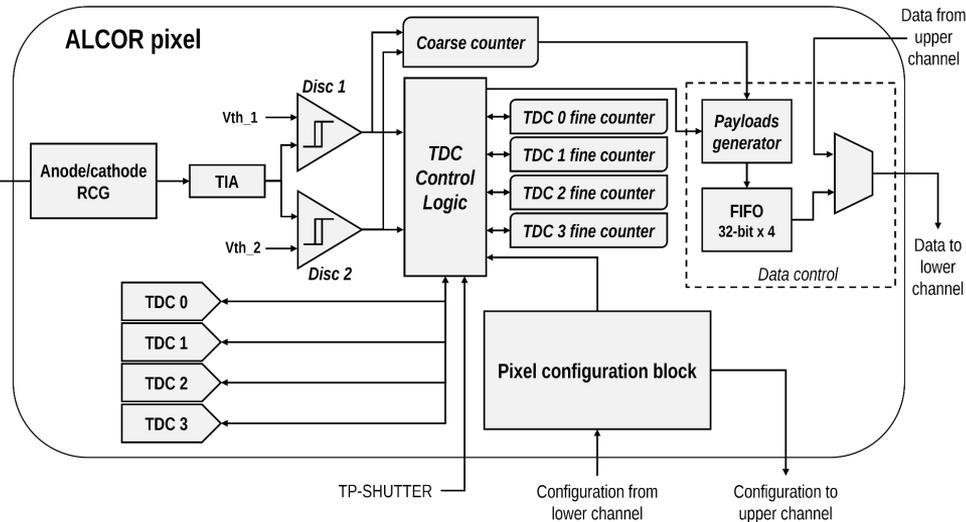
ALCOR: A Low Power Chip for Optical Sensor Readout

ALCOR-64 (ALCOR v3)

- **64-pixel** matrix (8x8) mixed-signal ASIC ($4.95 \times 7.02 \text{ mm}^2$)
- Single-photon time tagging + **Time-over-Threshold** or **Slew-Rate** measurements for **time walk correction**
- On-chip **signal amplification, conditioning** and **digitization**, 32-bit event word
- Trigger-less readout with fully digital output: **8 LVDS 394 MHz** DDR Tx links
- Power consumption **$\sim 12 \text{ mW/channel}$**
- **0.11 μm CMOS technology**
- ✓ **MPW tapeout on Apr 8th 2025**

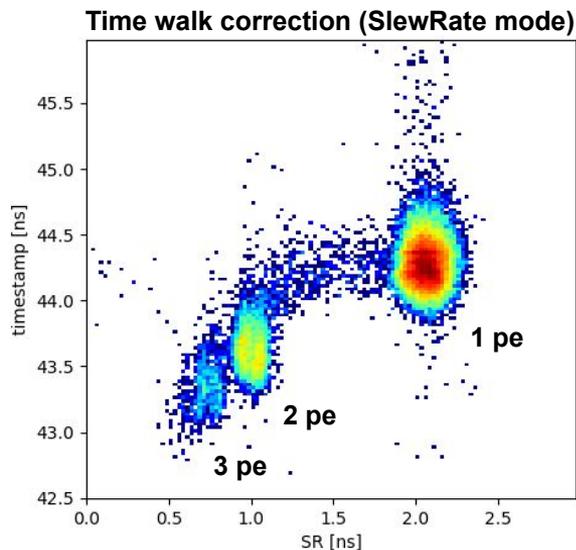
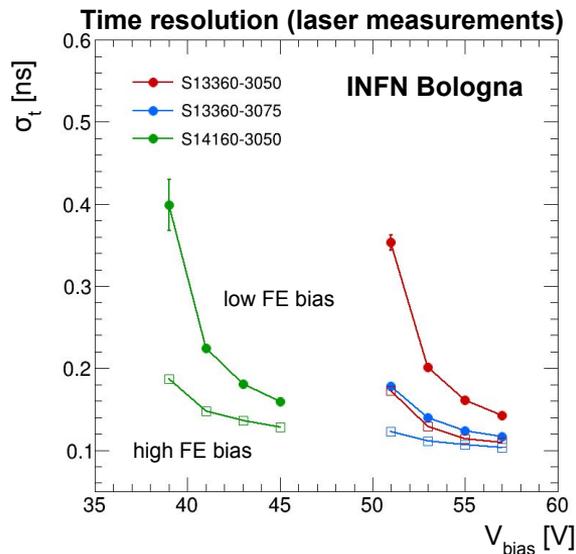


Pixel architecture

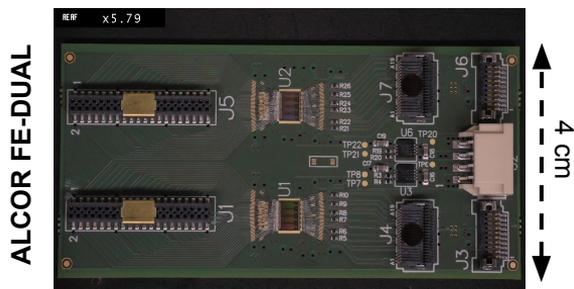


- **Dual-polarity RCG input stage** current conveyor ($Z_{in} = 10\text{-}20 \Omega$) + TIA with 4 gain settings $\rightarrow \sigma_t = 150 \text{ ps}$
- **2 leading edge discriminators** with independent (and per pixel) threshold settings (6-bit DAC) $\rightarrow V_{th} = 0.5 \text{ p.e.}$
- **4 TDCs** based on **analogue interpolation** with **20-40 ps** time-bin (at 394 MHz clock frequency)
- Pixel control logic handles TDC operation, pixel configuration, operating mode and data transmission
- **TP-Shutter** to inhibit events digitization (asynchronous with ns time window in **ALCOR-64**) and suppress out-of-time SiPM DCR hits

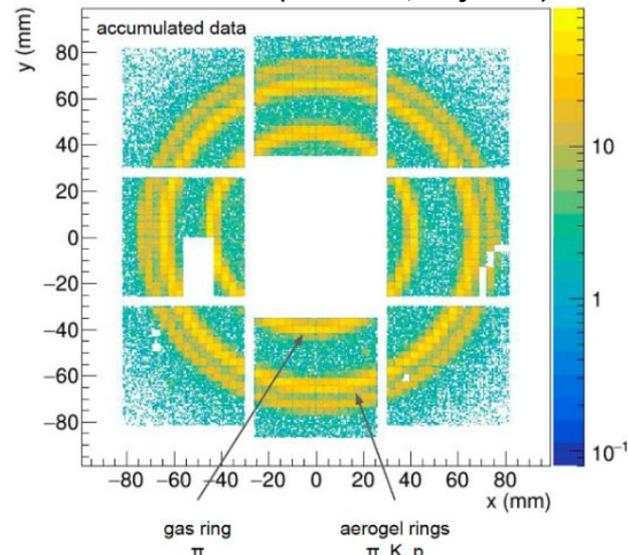
ALCOR v2 results



- Better **time resolution** with 75 μm SPADs, comfortably below $\sigma_t = 150$ ps also at low V_{bias}
- **Time walk correction:** SlewRate mode provides good separation between afterpulses (slow-rise time, large ToT) and cross-talk (fast rise-time, large ToT)



Beam test with prototype dRICH and PDUs (CERN-PS, May 2024)

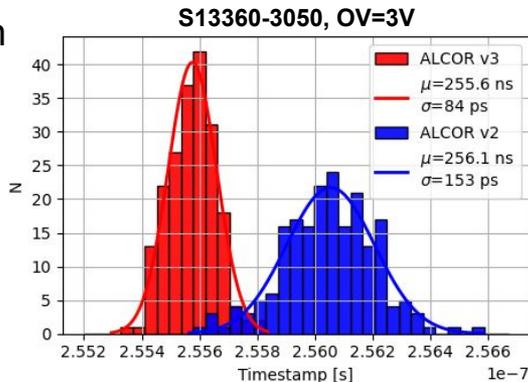


32 FE-DUAL (64 ALCOR, **2048 channels**)
 SiPM: HPK **S13360-3050** and
S13360-3075 ($3 \times 3 \text{ mm}^2$, $T = -30/-40^\circ\text{C}$)

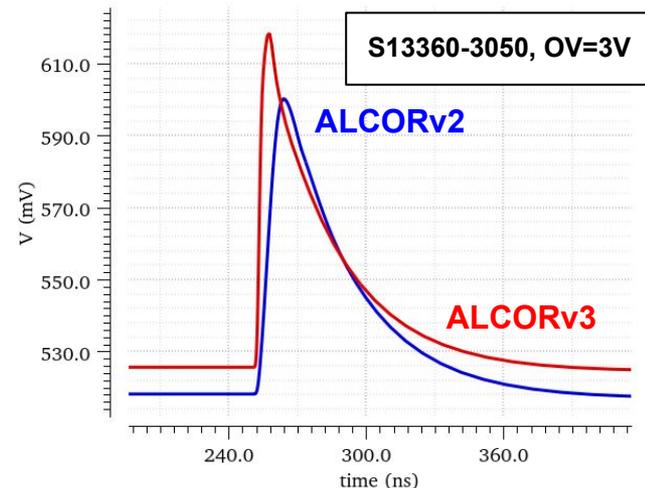
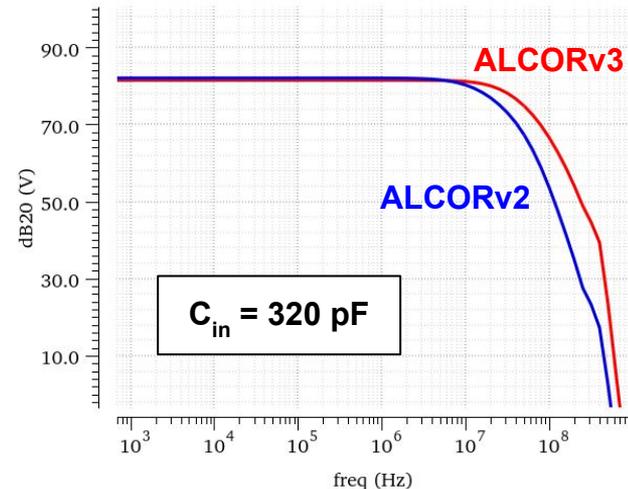
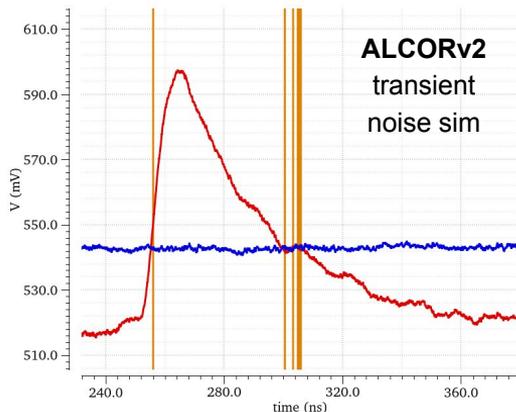
ALCOR v3 - analogue

Small revisions on ALCOR FE design

- **Increased amplifier bandwidth** to improve time resolution
 - transient noise simulations
 - $V_{th} = 0.5$ p.e.
 - **jitter: 153 ps \rightarrow 84 ps**



- **Discriminator with programmable hysteresis** to avoid re-triggering on slow tail with low thresholds



ePIC streaming data acquisition system (no traditional hardware trigger)

- Operation at **0.5 p.e. threshold** → DCR noise up to **300 kHz/channel** (at max SiPM radiation damage)
- **Digital shutter**: “inhibit” pixel digital logic to suppress out-of-gate DCR hits and **reduce data throughput**
- ~10.2 ns bunch crossing, ~300 ps bunch length, select **2-3 ns time window**
- Asynchronous digital shutter implemented in ALCOR v3 pixel logic using external test-pulse signal
- **Programmable delay chain**: 4 configuration bits at channel-level (LSB = 350 ps) and at the chip periphery (LSB = 100 ps) to adjust offsets between different pixels and columns
- Shutter needed only when DCR becomes higher due to SiPMs taking radiation damage over time
→ use first period of ePIC data taking to optimize **shutter calibration** (understand electronics and physics contributions)

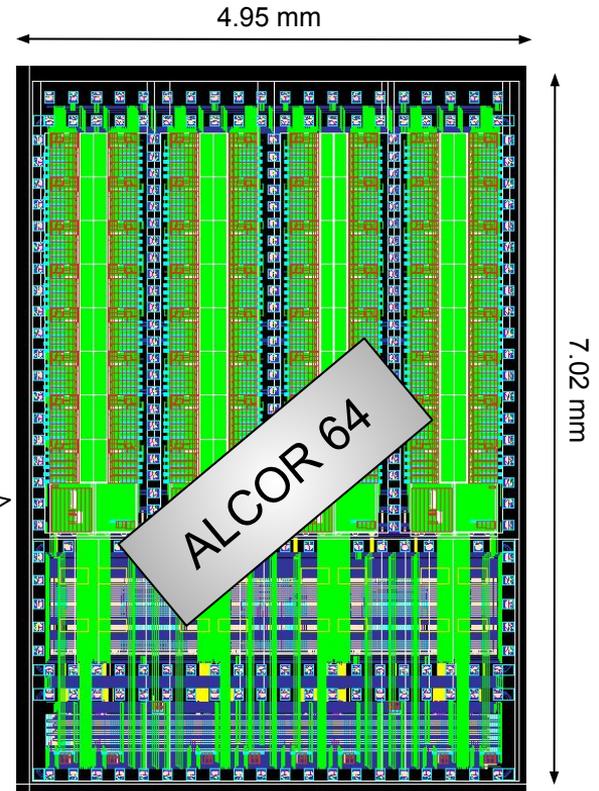
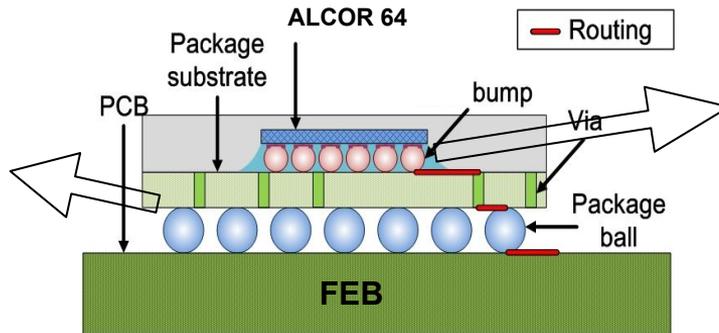
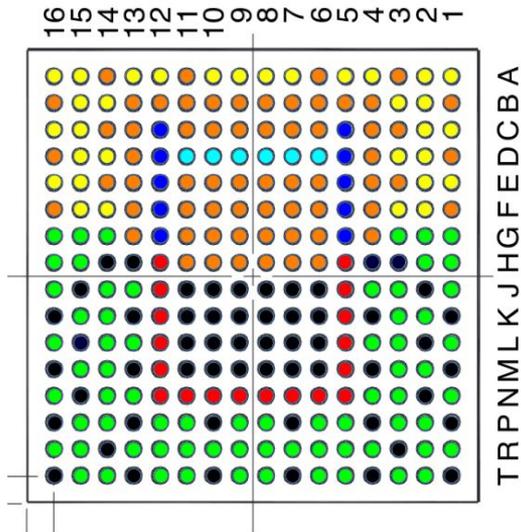
Possible problem of an **excessive data bandwidth (> 1 Tbps)** for the ePIC DAQ system when **DCR** approaches **300 kHz**. Two complementary approaches are being considered:

1. **dRICH interaction tagger** (INFN Genova): dedicated sub-detector (scintillating fibers + SiPM + ALCOR based readout) tagging relevant interactions → S. Vallarino talk
2. **ML online data filtering** (INFN Roma) at sub-detector level (FELIX DAMs) against pure dark-count event
→ C. Rossi talk

ALCOR BGA package

FC-BGA: flip-chip ball grid array

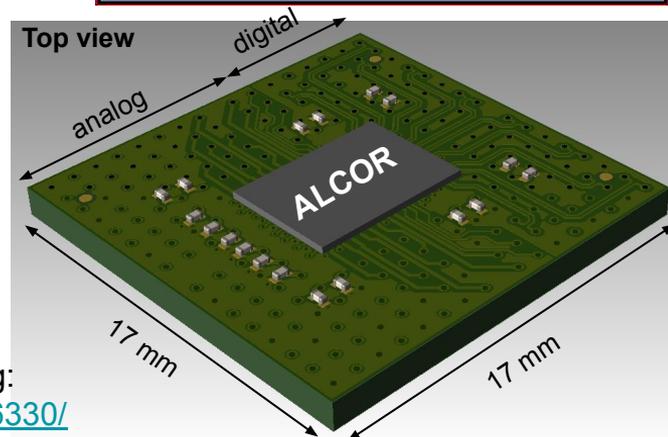
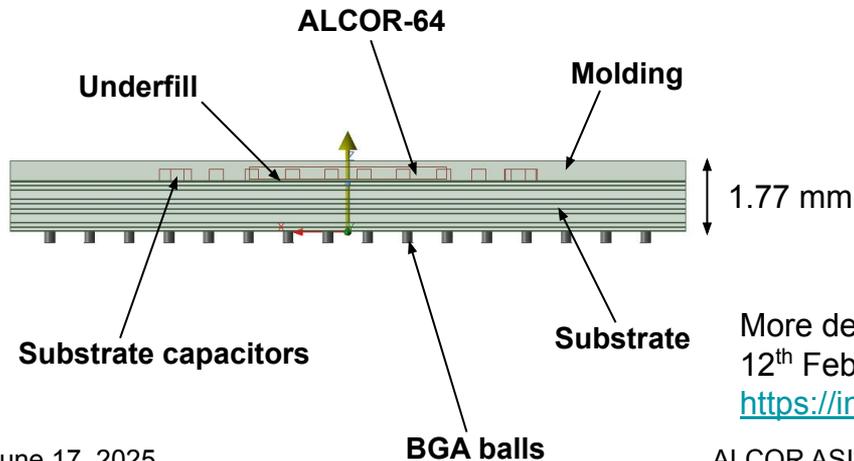
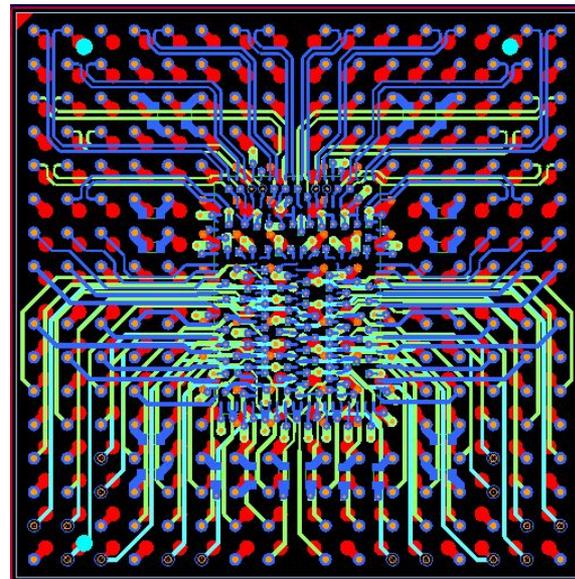
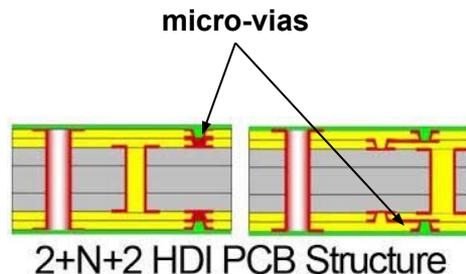
- BGA substrate designed by INFN Torino (M. Mignone)
- Substrate production, flip-chip assembly and packaging done by I-Tronics (<https://www.itronics-sg.com/>)



ALCOR BGA

- BGA 256 Ball 17x17mm 1mm-pitch
- BT-Epoxy
- 10 Layers (2+N+2)
- Thickness: 1.27 mm
- Decoupling capacitors (0201)
- Design completed on Jan 2025
- Verification: electrical and thermal simulations

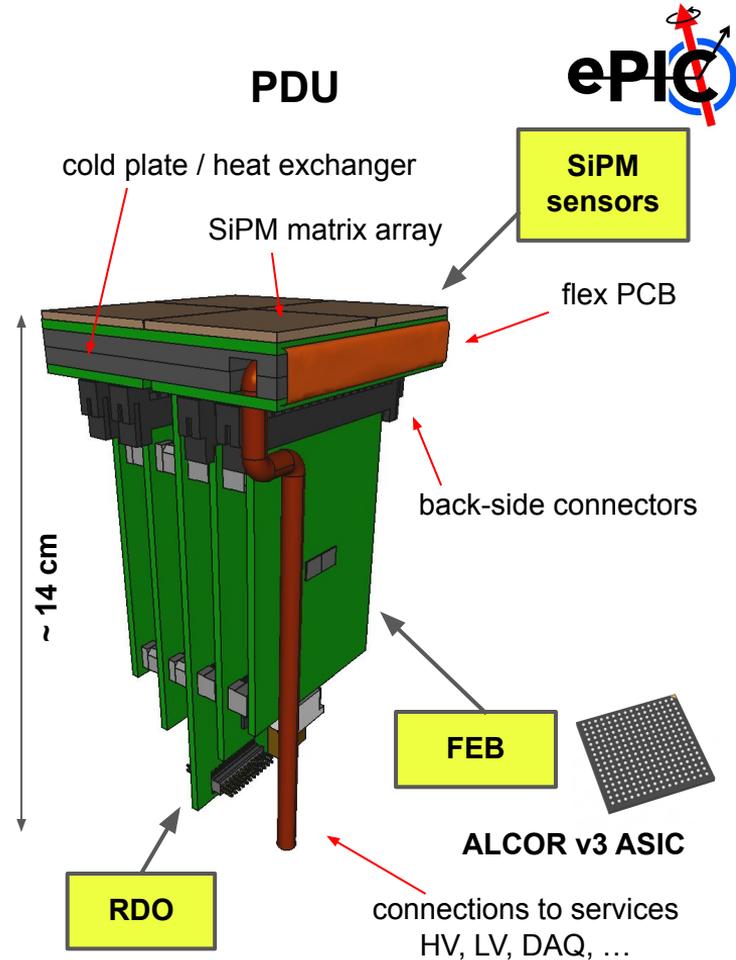
✓ **Sent for production on Apr 2025**



More details presented at the
12th Feb 2025 dRICH Meeting:
<https://indico.bnl.gov/event/26330/>

dRICH ALCOR FEB

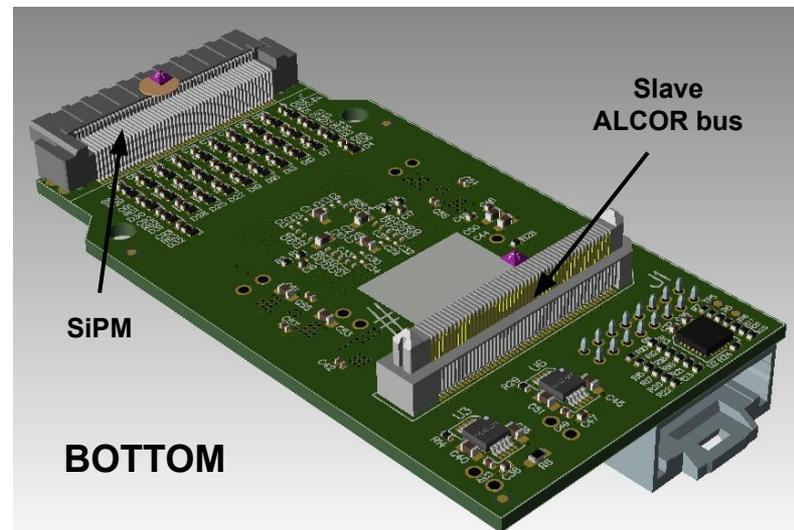
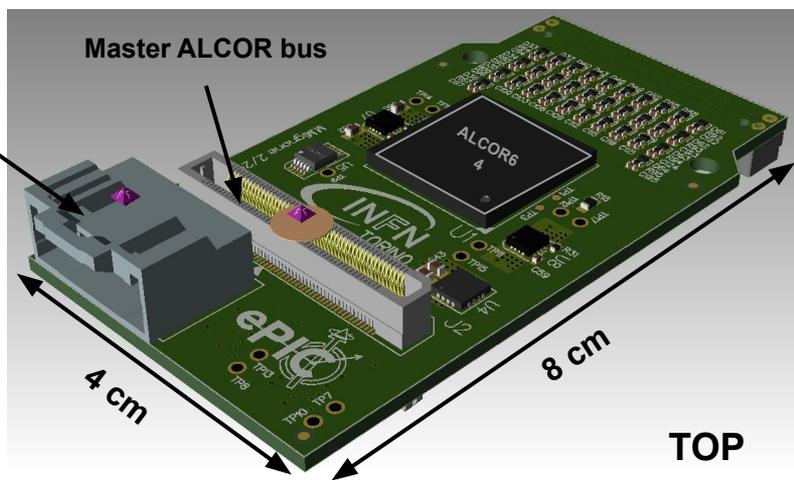
- **4 FEBs** in each PDU (**256** readout **channels**), managed by **1 RDO** (INFN Bologna)
- FEB designed by INFN Torino (M. Mignone), close cooperation with Bologna-Ferrara colleagues to match *RDO design, SiPMs requirements and space constraints*
- 2 slightly different FEB versions, they share the ALCOR BUS connector (interface with RDO):
 - **Master**: internal FEB
 - **Slave**: external FEB



dRICH ALCOR FEB

- I-Tera MT40, 10 layers
 - Connectors towards RDO (ALCOR bus), detector (SiPM carrier), off-detector (Services)
 - Linear Regulators, current monitors, I2C expander, AC-coupling + annealing circuitry
 - Power segmentation: LV → 64 ch., HV → 32 ch.
- Dedicated PCB section for SiPMs HV routing
- $2 V_{\text{bias/annealing}}$ PCB layers/sections, each serving 32 SiPMs
 - **SiPM online annealing**: forward-bias, $I = 60\text{-}100 \text{ mA}$ to reach $T = 150^\circ\text{C}$ on SiPM matrix board
 - Expected FEB temperatures **up to 100°C**
 - **Annealing diodes** to provide path to ground for SiPM annealing current → trade-off between C_{in} and power

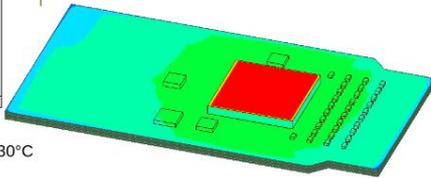
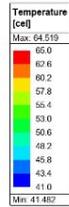
✓ **Design completed on May 2025**



Thermal simulations and SMA-annealing FEB

Preliminary and simplified thermal simulations of one FEB board during normal operations and while performing annealing embedded in a **static $T = 30^{\circ}\text{C}$ ambient** → need **simulations with realistic detector box cooling**

Normal mode (ALCOR ON)



$T_{\text{amb}} = 30^{\circ}\text{C}$

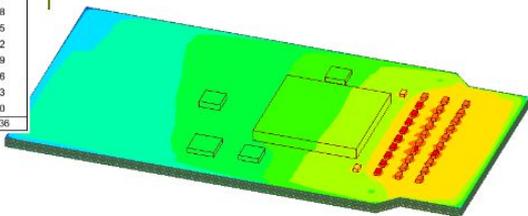
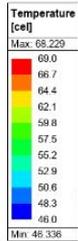
-Preg + Pbuffer
-Palc64 = 965mW

-BGA
 $T_j = 64.8^{\circ}\text{C}$

-PCB(Top):
 $T_{\text{max}} = 53^{\circ}\text{C}$
 $T_{\text{mean}} = 50^{\circ}\text{C}$

-PCB(Bot):
 $T_{\text{max}} = 52.7^{\circ}\text{C}$
 $T_{\text{mean}} = 50^{\circ}\text{C}$

Annealing mode ($V_f = 0.43 \text{ V @ } 70^{\circ}\text{C} \times 60 \text{ mA} \rightarrow 26 \text{ mW}$)



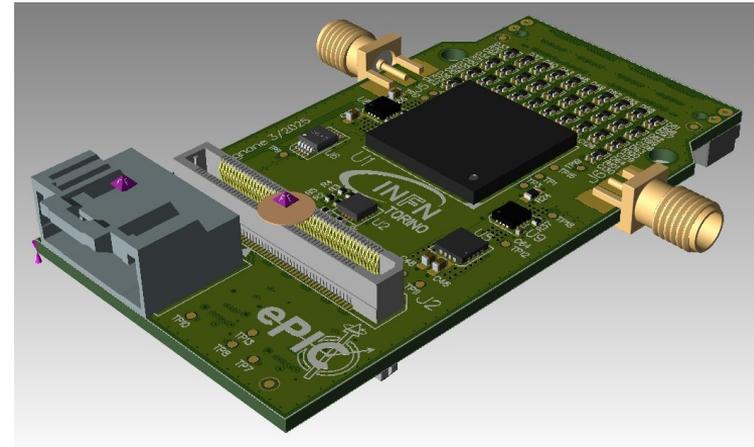
$T_{\text{amb}} = 30^{\circ}\text{C}$

-DIODI:
 $64 \times 26 \text{ mW}$
 $T_{\text{max}} = 68^{\circ}\text{C}$

-BGA:
 $T_{\text{max}} = 61^{\circ}\text{C}$
 $T_{\text{mean}} = 59^{\circ}\text{C}$

-PCB(Top):
 $T_{\text{max}} = 67^{\circ}\text{C}$
 $T_{\text{mean}} = 57^{\circ}\text{C}$

-PCB(Bot):
 $T_{\text{max}} = 68^{\circ}\text{C}$
 $T_{\text{mean}} = 57^{\circ}\text{C}$

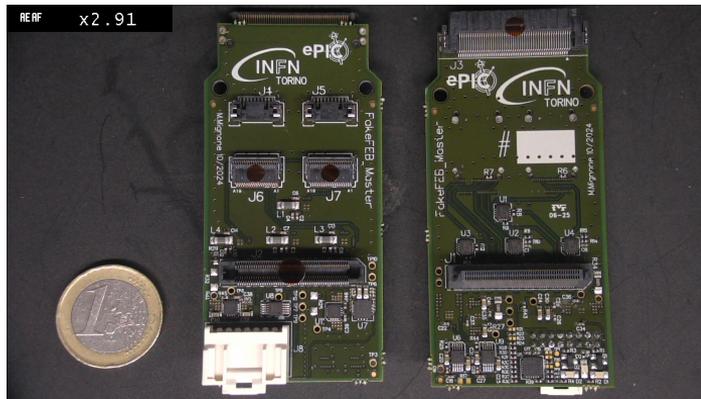


FEB prototype to test SiPM annealing

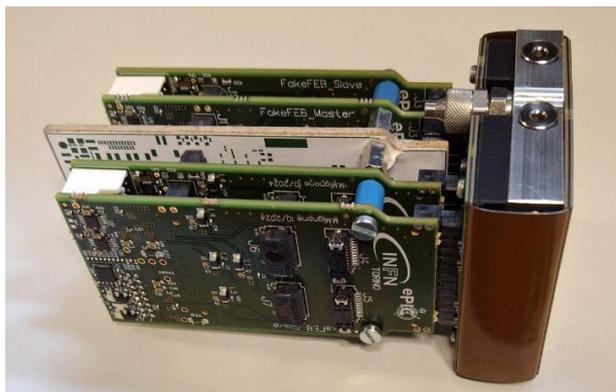
- like final FEB, with all annealing circuitry
 - added **2 SMA connectors** to inspect SiPM signals on scope → can be used also without ALCOR-64
- ✓ **Purchase order issued 2-3 weeks ago**

“Fake” FEB

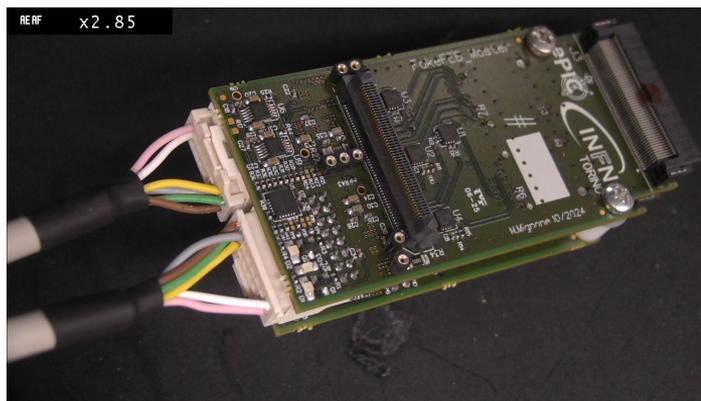
- Support **2025 dRICH activities** (Nov 2025 beamtest) when final FEB and ALCOR v3 are not available yet, allowing **test of RDO with current ALCOR-FE-DUAL** boards (with FireFly cables)
- Designed using specifications of final FEB: same space constraints, very similar components and same connectors (SiPM, RDO, and services)
- ✓ 10+10 “Fake” FEBs received mid March



- ✓ Assembly of first “Fake” PDU in Bologna last week



“Fake” PDU = 4 “Fake” FEBs + 1 RDO



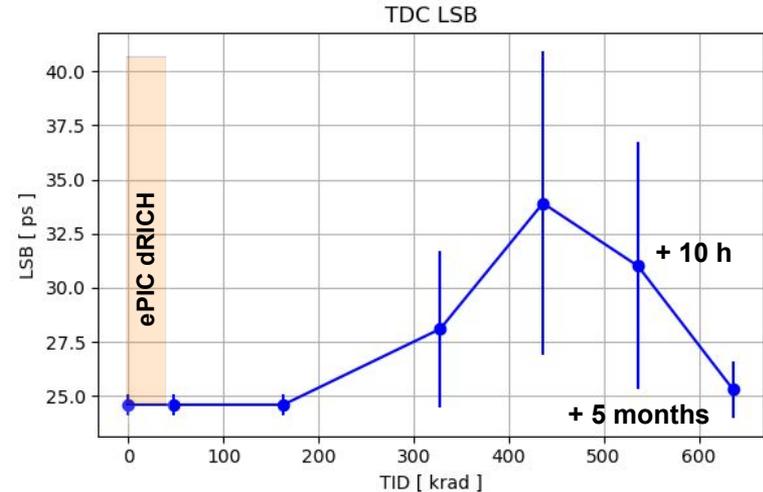
Radiation tolerance

The dRICH-PDUs are in a moderately hostile radiation environment

- Φ (p+n > 20 MeV) = 200 Hz/cm²
 - TID \approx 2.3 krad (for 1000 fb⁻¹)
- } safety factor of 5 included

➤ Irradiation tests campaign: SEU/SEL and TID tests at Centro of Proton-Therapy in Trento with ALCOR-32 in Jul 2024 and Dec 2024

- **Technology is sufficiently radiation tolerant** to be used in the ePIC dRICH environment
- **SEU rate is within the expected manageable levels:** in ALCOR v3 TMR SEU protection added also for periphery registers, Hamming code SEU protection for FSMs
- **Other FEB components need be tested and validated**



Detailed results presented at the 29th Jan 2025
dRICH Meeting: <https://indico.bnl.gov/event/26313/>



towards construction →

2022

electronics v1

ALCOR v1



2023

electronics v2

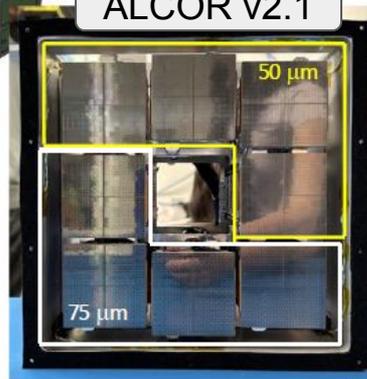
ALCOR v2



2024

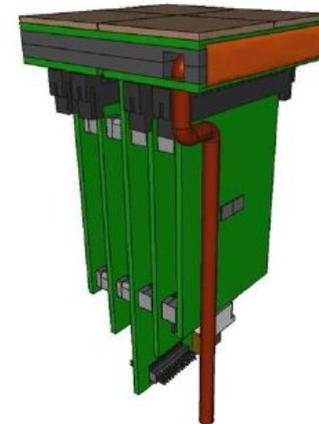
electronics v2.1

ALCOR v2.1

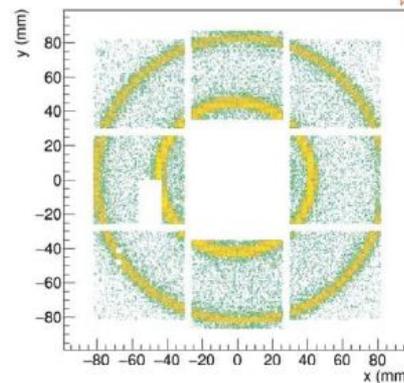
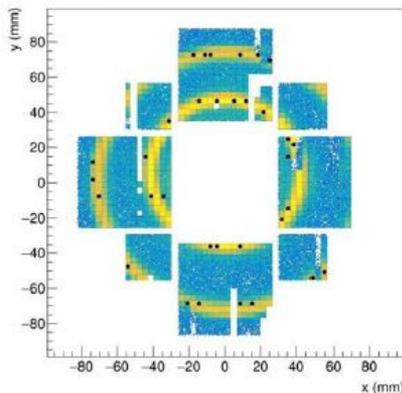
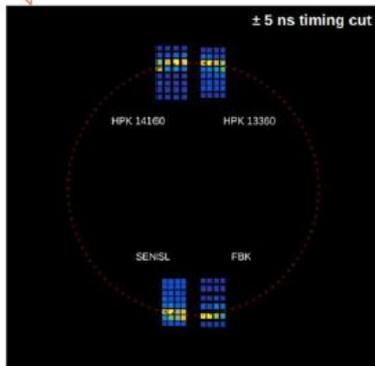


2025/26

electronics v3



ALCOR 32 ch



Full size engineering test article

2025 + SiPM carrier v3
+ RDO

2026 + ALCOR 64ch
+ FEB 64

Next steps towards production



ALCOR-64 MPW tapeout on Apr 2025, 50 singulated dies expected for Sep 2025, then packaging

ALCOR-64 testing

- **End of 2025:** test ALCOR-64 from MPW → first **electrical characterization** in Torino
- **Start of 2026:** tests with **SiPM sensors** and RDO together with Bologna → fully assembled PDU
- Final validation at **beam-test during 2026**

Preparation for production

- Mid 2026: design revision

Start of production

- **End 2026 - Start 2027: Engineering run**

This is the **best case scenario**, we have contingency time for extra MPW run in 2026 and production during 2027

FEB and ALCOR are part of INFN IKC

- The whole production batch will be delivered in Italy for QA and integration, with fully assembled detector boxes shipped to BNL
- Updating quotations for ALCOR engineering run, packaging and FEB production

QA is organized to allow essential acceptance tests on 100% of components plus in-depth sample characterization (1-2%)

- **Acceptance tests:** power-on, current absorption, configuration, data alignment, TDC scan, Vth scan
- **In-depth sample characterization:** SiPM DCR scan, laser measurements (jitter, shutter)
- Special test board card will be developed to test ALCOR standalone (also without RDO) and support readout of 1 SiPM matrix
- Different options are currently being evaluated: **in-house testing** (parallel QA stations) or **external company** (previous experience: CMS ECAL ASIC: 80k LiTE-DTU chips being tested by [Microtest](#))
 - N. FEBs: 4992 → N. ALCOR: 4992 (increase number to include production phase risk mitigation)
 - 7500 ALCOR → 85% yield → 6375 ALCOR
 - **7500 ASIC · 8 min./ALCOR = 60000 min. = 1000 h → 30 weeks → 7-8 months**
- After **ALCOR/FEB validation**, FEB will be moved to **PDU assembly line**: FE electronics tested again after being integrated inside PDU (4 FEBs + 1 RDO + SiPM matrices)

Summary



- ALCOR is a 64-channel mixed-signal ASIC adopted for the readout of the SiPM sensors for the ePIC dRICH detector
- ALCOR has been extensively used within the dRICH Collaboration in the last 4-5 years: several laboratory and beam tests demonstrated the ALCOR-based readout capability to measure single photons with good time resolution and rate capability
- ALCOR v3 is the first version to include all features and specifications required for the ePIC dRICH:
 - 64 channels, BGA package
 - Digital shutter to reduce data throughput, 394.08 MHz clock frequency
 - ASIC tape-out in Apr 2025
- Upgrades of DAQ systems to test ALCOR-64 ongoing → define requirements for QA/QC setup

Backup Slides



Istituto Nazionale di Fisica Nucleare
SEZIONE DI TORINO

C. Alice, A. Bortone, M. Chiosso, F. Cossio, M. D. Da Rocha Rolo, G. Dellacasa,
C. Ferrero, D. Giordano, M. Mignone, A. Rivetti, M. Ruspa, R. Wheadon

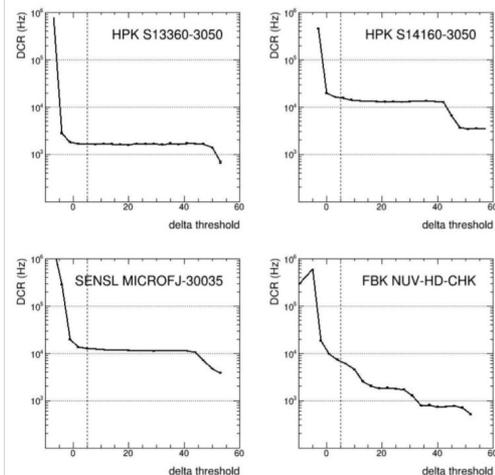
fcossio@to.infn.it

Developed by INFN for the readout of SiPMs at 77K, in the framework of Darkside (Dec 2019)

- Pixel matrix layout to explore solutions towards the development of an active silicon interposer for the integration of large area SiPMs for future massive frontier LAr Dark Matter Experiments



Extensively used within the EIC dRICH Collaboration during 2021-2022

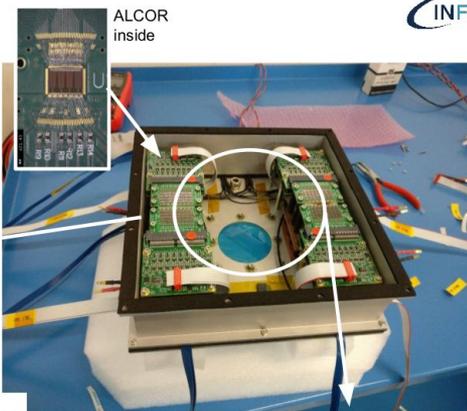


2022 test beam at CERN-PS

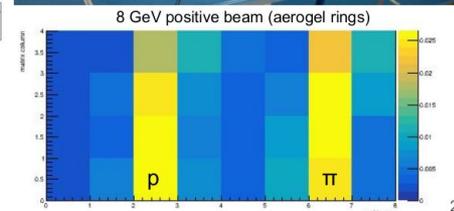
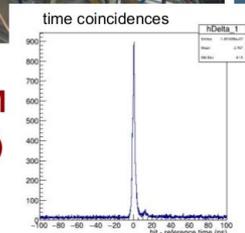
dRICH prototipe on PS beamline with SiPM-ALCOR box



beamline shared with LAPPD test



successful operation of SiPM irradiated (with protons up to 10^{16}) and annealed (in oven at 150 C)



ALCOR v2

- MPW, submitted in Dec 2022
- 60 chips, received in **June 2023**
- **First version developed for ePIC**, includes new features targeted for ePIC dRICH and bug fixes:
 - ✓ TDC logic critical error at high rates solved also for DCR rate at room temperature
 - ✓ New FE gain settings more suited for single photon applications
 - ✓ On-chip test-pulse also for ePIC SiPM polarity
- Successfully validated in **2023 beam test**: 20 FE-DUAL (40 ALCOR v2.0, **1280 channels**)

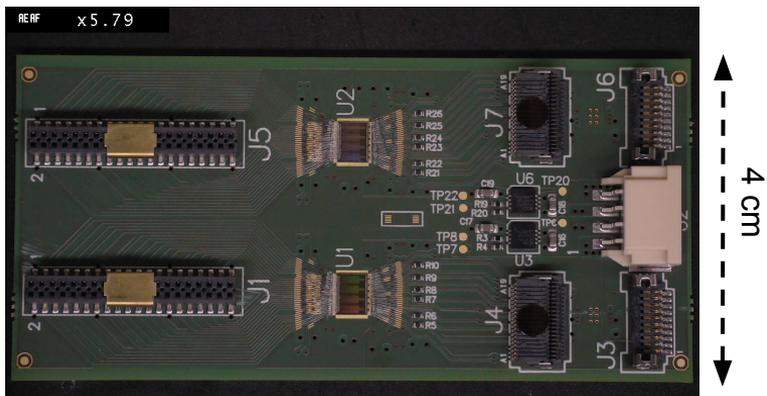
ALCOR v2.1

- INFN internal engineering run, chips received in **Jan 2024**
- Version currently used, includes small bug fixes w.r.t. ALCOR v2 (TDC Tfine ambiguity)
- Very high number of chips available to increase instrumented area for dRICH prototype and assemble other test setups
- Successfully validated in **2024 beam test**: 32 FE-DUAL (64 ALCOR v2.1, **2048 channels**)

dRICH prototype readout system

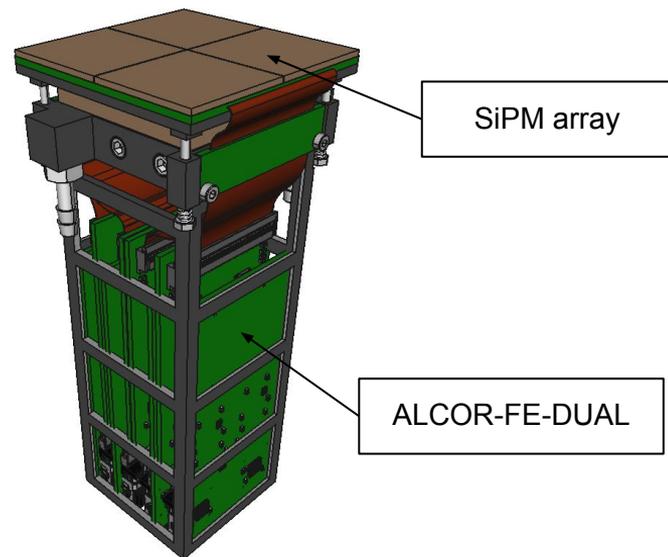
ALCOR-FE-DUAL board

- Two **32-channel** ALCOR ASICs **wire-bonded** on the PCB
- **4 ALCOR-FE-DUAL** boards for each PDU (**256 channels**)
- System used for **2023-2024** ePIC dRICH beam tests



Designed using specifications close to final FEB: very similar space constraints and same number of channels (64)

ePIC dRICH Prototype photodetector unit (PDU)



Prototype to test and validate PDU geometry and functionality (no RDO)

ALCOR v3 - digital interface

- Clock frequency: **394.1 MHz** (4x EIC clock: 98.52525 MHz)
- **8 LVDS Tx links**: one for each column, DDR output at **788 Mb/s**
- Data format
 - **32-bit words** with **8b/10b encoding** (2x event words in ToT/SR mode)
 - Frames with *header + data + trailer*
 - Frame duration set by *coarse counter roll-over* or *New Orbit reset*
- External **reset** with 3 different features depending on signal width:
 - 24-31 xCLK: **Hard Reset**
 - 16-23 xCLK: **Start** (Frame Counter = 0 and Coarse Counter = 0)
 - 8-15 xCLK: **New Orbit** (Frame Counter +1 and Coarse Counter = 0) → forces a *rollover* condition (ALCOR rollover = 2^{15} clk cycles \approx 83 μ s, EIC orbit period \approx 12.8 us)
- **Test Pulse**: analogue FE injection and TDC calibration; also used for **shutter** signal; propagated from EoC to each pixel
- **SPI** interface for registers configuration

FIFO position	Data (32-bit word)
1	K28.0 (Frame header)
2	Frame number
3 + ...	Event words Column X
n	K28.2 (Frame trailer)
n+1	Frame info (frame_len, ev_lost)
n+2	<i>K28.3 (Status header)</i>
n+3	<i>Status words Column X (8x)</i>
n+11	<i>End of Column status word</i>
n+12	K28.4 (Checksum header)
n+13	CRC value

Summary of key differences between ALCOR versions



	ALCOR-32	ALCOR-64
Channels	32	64
Die size	4.95 x 3.78 mm ²	4.95 x 7.02 mm ²
Assembly	Wire-bonded on PCB	BGA package
Clock frequency	320 MHz	394.08 MHz
Time resolution	< 200 ps	< 150 ps
Shutter	synchronous, width > 100 ns	asynchronous, width ~ 2-3 ns
SEU protection	only pixels	pixels + EoC
Dataframe duration	2 ¹⁵ clock cycles	2 ¹⁵ clock cycles or user defined
Power consumption	10 mW/ch	12 mW/ch

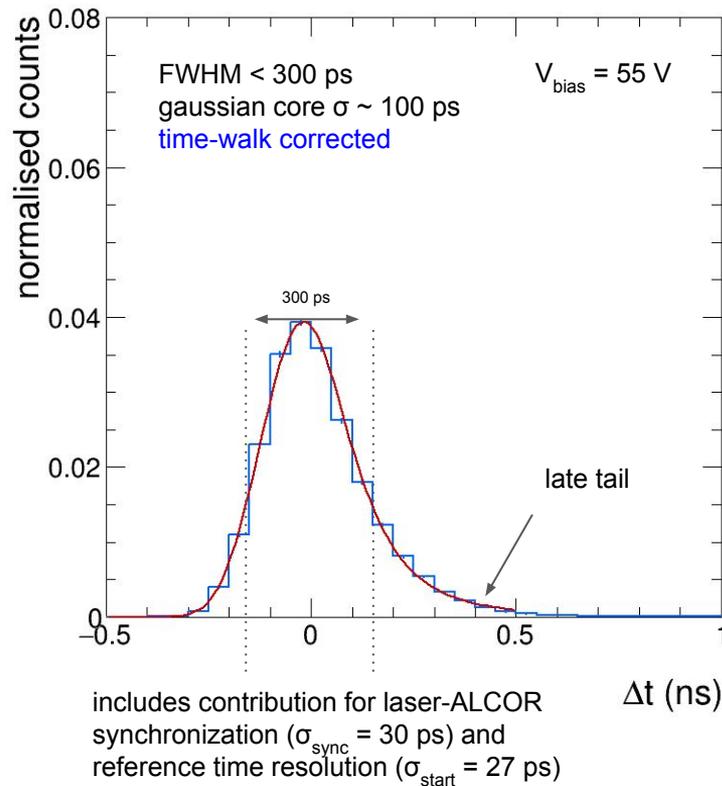
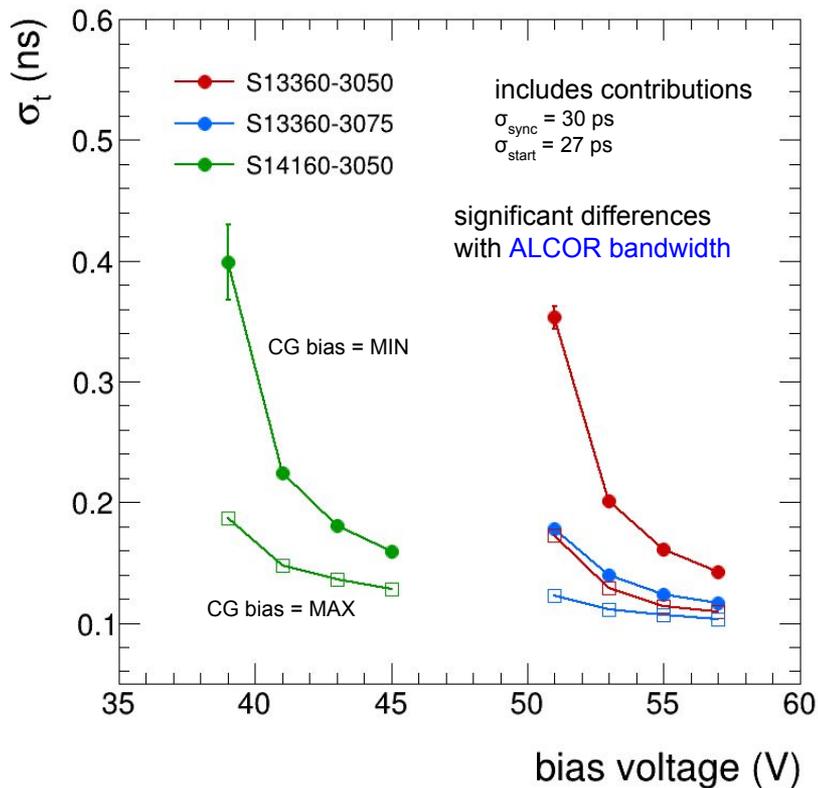
Summary of ALCOR specs for the dRICH detector



Function	Digitization from SiPMs with 1 p.e. sensitivity
Mode	Single-photon tagging or time and charge
Tech Node	110 nm CMOS
Channels	64 (8x8), dual polarity
Cdin	<1 nF
Digitization	20-40 ps TDCs, ToA + ToT; Timing < 150 ps
Shutter	Width: 2 - 3 ns, programmable latency
Input Rate	<2.4 MHz (up to 5 MHz on single channel)
Clock	394.08 MHz operation from BX 98.52 MHz
Links	788 Mbps LVDS, SPI configuration
Power	12 mW/ch
Package	BGA
Rad Tolerance	Radiation hard

→ 788 Mbps / (40 bits * 8 pixels) = 2.4 MHz
(assuming no extra control words)

Laser timing measurements

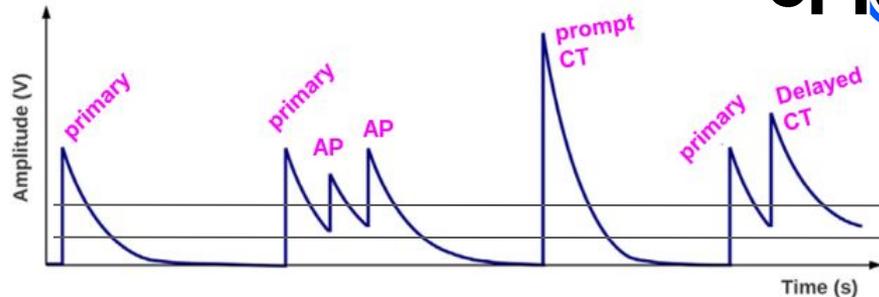


- Better time resolution with **75 μm SPADs**
- Comfortably below **$\sigma_t = 150$ ps** also at low Vbias

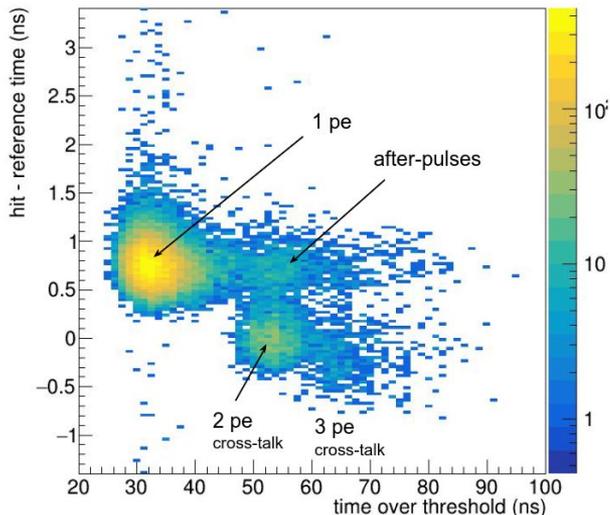
Time walk correction



Time walk correction needed to improve overall time resolution → studies with laser setup using **ToT** and **SlewRate** measurements



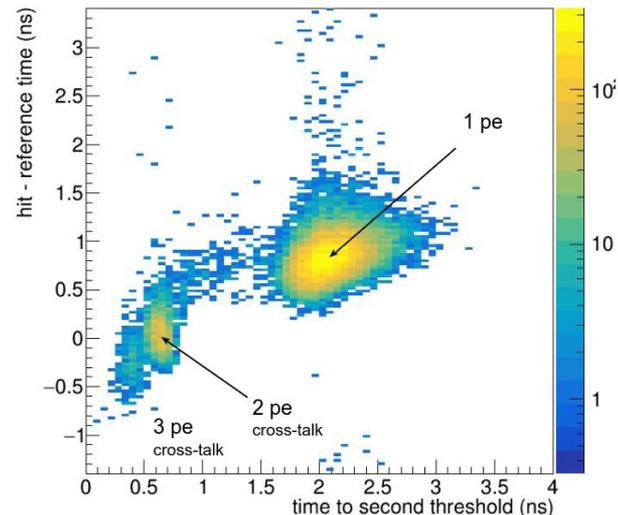
ALCOR ToT mode



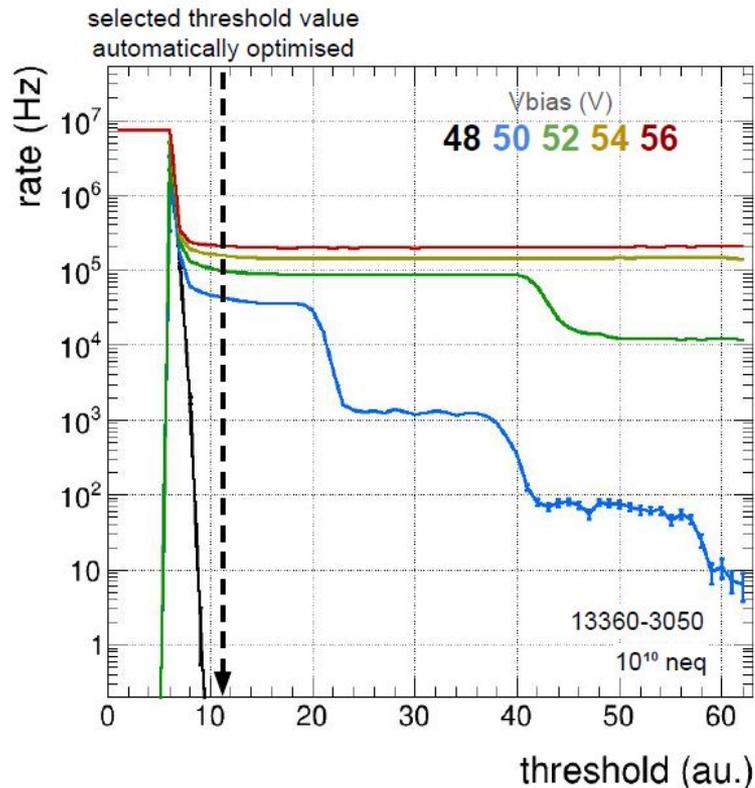
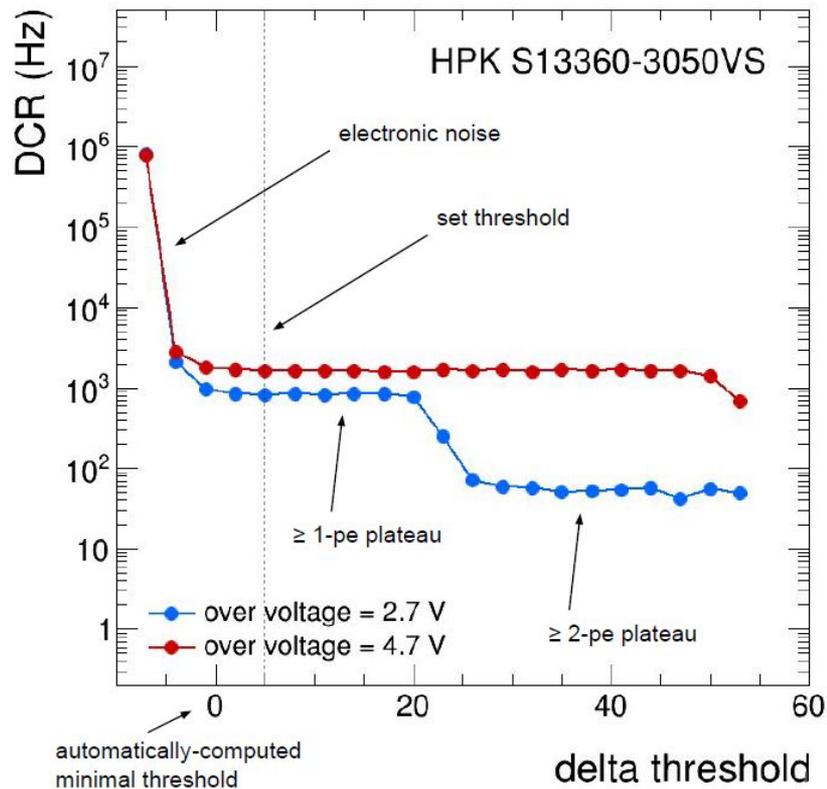
✗ **ToT mode** cannot distinguish between afterpulses (slow-rise time, large ToT) and cross-talk (fast rise-time, large ToT)

✓ **SR mode** provides better separation

ALCOR slew-rate mode



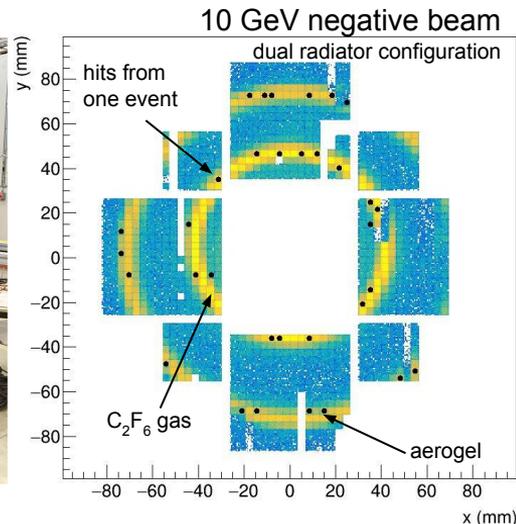
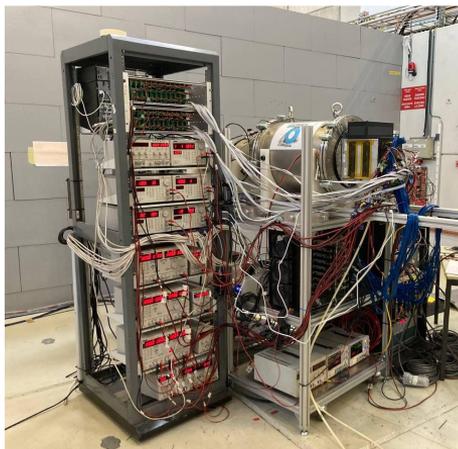
ALCOR threshold scan



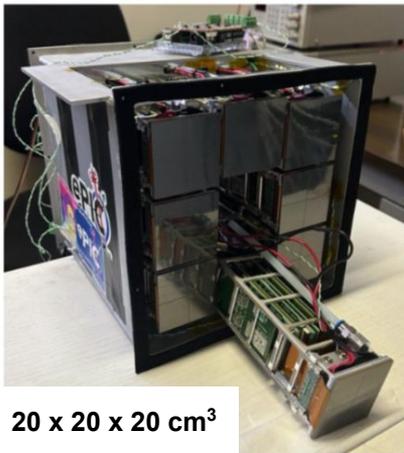
Beam tests at CERN-PS

Successful beam tests with prototype dRICH and PDUs (CERN-PS, October 2023, May 2024)

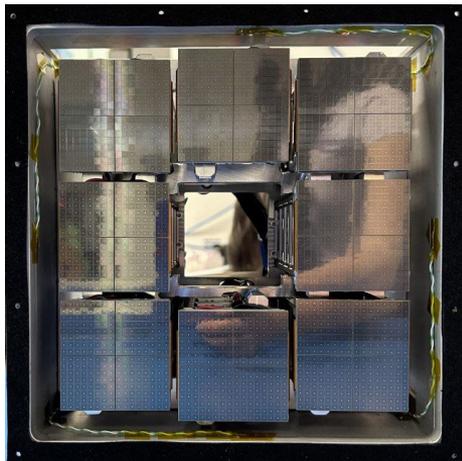
- HPK S13360-3050 and S13360-3075 ($3 \times 3 \text{ mm}^2$, $T = -30/-40^\circ\text{C}$)
- 32 FE-DUAL (64 ALCOR v2.1, **2048 channels**)
- DAQ: Xilinx Kintex 7 KC705



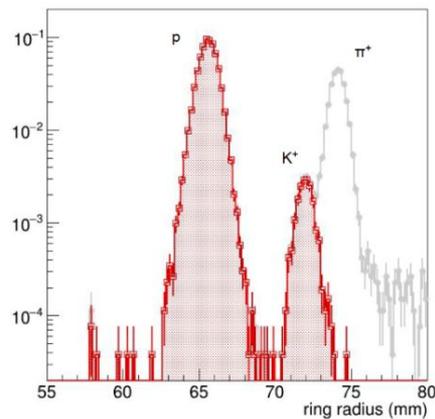
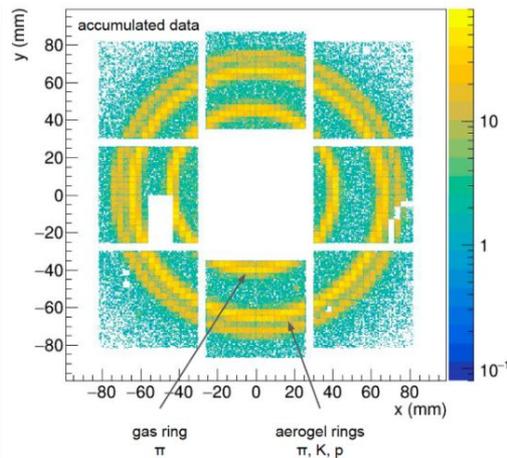
Realistic detector plane based on dRICH PDUs **Validated**



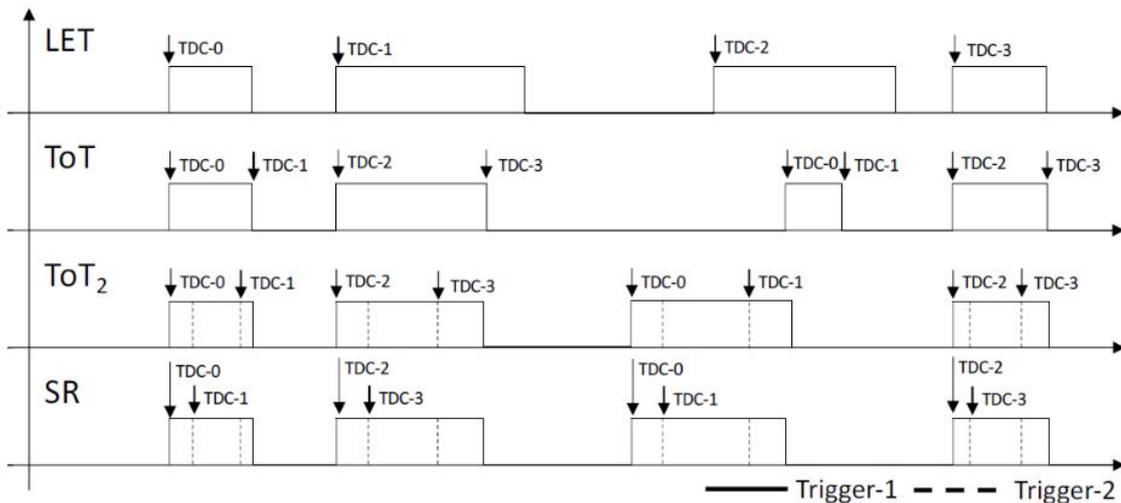
20 x 20 x 20 cm³



dRICH prototype got the expected performance and radiator interplay



ALCOR pixel operating modes



4 operating modes:

- **LET:** leading edge measurement
- **ToT:** Time-over-Threshold measurement using the first discriminator for both edges
- **ToT₂:** Time-over-Threshold measurement using both discriminators
- **SR:** slew-rate measurement

Each mode can be set to:

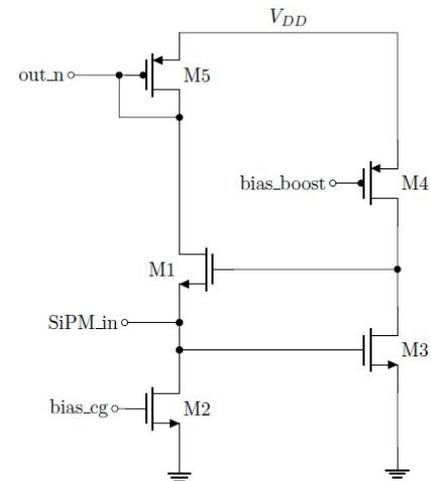
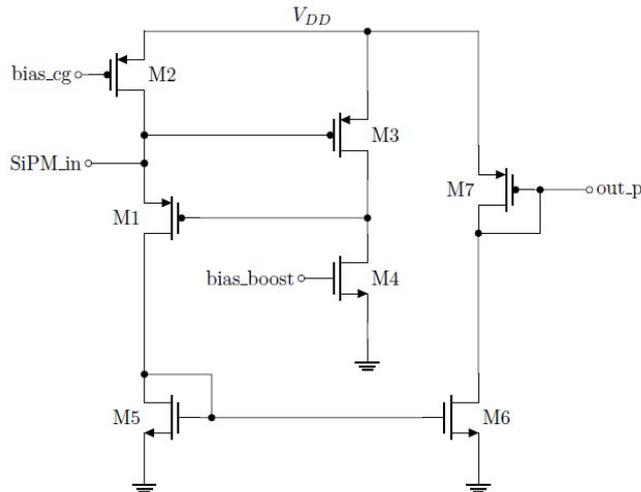
- **FE:** normal operation mode
- **FE_TP:** send test-pulse to analogue front-end
- **TDC_TP:** send test-pulse to pixel control logic to test and calibrate TDCs (bypass front-end)

Each pixel can also be disabled

ALCOR Front-End

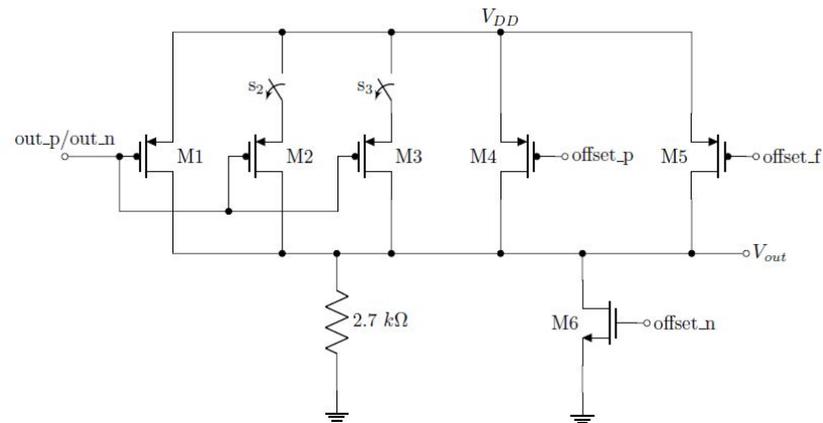
Input stage

- Dual-polarity RCG current conveyor
- Programmable bias currents: CG (30-100 μA) and BOOST (1-4 mA)
- $Z_{in} \sim 10\text{-}20 \Omega$



Output stage

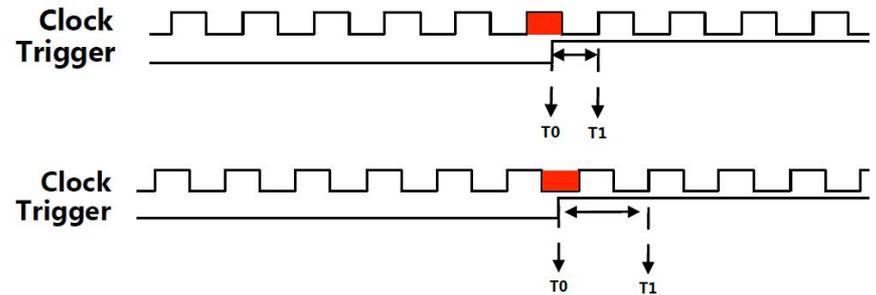
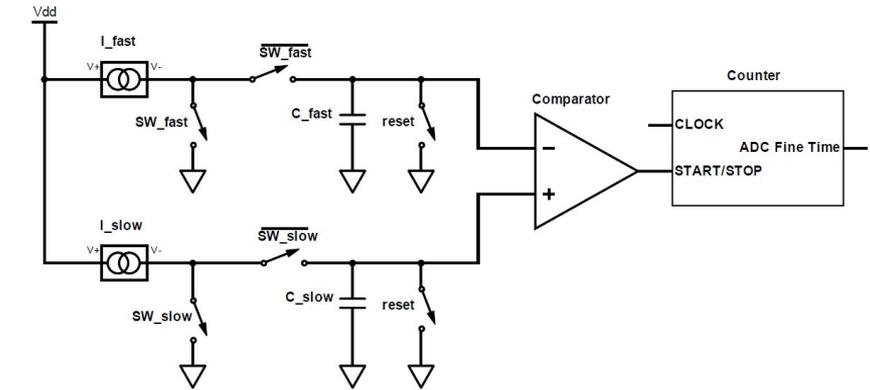
- TIA gain: 2.7 k Ω
- 4 gain settings: 1/3, 4/3, 7/3 and 10/3
- DC coupled: baseline compensation based on gain and CG bias current settings + fine offset adjustment (3-bit)



Time to Digital Conversion



- Coarse time: 15-bit clock counter
- Time conversion performed by **TDC** based on **analogue interpolation** (9-bit fine time):
 - **fast ramp**: constant current to charge C_{fast} → measure phase between event trigger and clock
 - **slow ramp**: smaller constant current to charge C_{slow} → counts clock cycles until C_{slow} and C_{fast} are equal
- I.F. 64 or 128 → **LSB = 20-40 ps @394 MHz**
- Measured time interval: 0.5 - 1.5 clk period
- TDC conversion time: [160, 500] ns
- 4 TDCs per pixel for **event derandomization**



Shutter mixed-signal simulation

Shutter: periodic test-pulse (width = 2.5 ns)

Spectre netlist simulates different SiPM SPADs:

- Each **SPAD** is modeled with a current pulse generator, each with a different period
- **Real photons:** current pulse generators are synchronized with the shutter signal
- **Dark-count signals:** current pulse generators are not synchronized

Decode data, calibrate TDCs (from DCR asynchronous signals),
extract ToA, compare with input netlist to evaluate shutter efficiency:

Total simulation time = 19532690.640 ns

Total number of dark counts = 10006

Dark count rate = 512.269 kHz

Dark counts cut by shutter: 8411

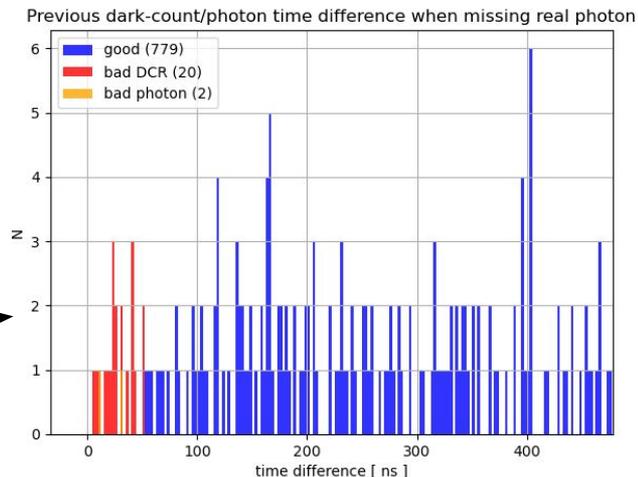
Dark counts passed through shutter: 1595

Shutter cut: 84.06%

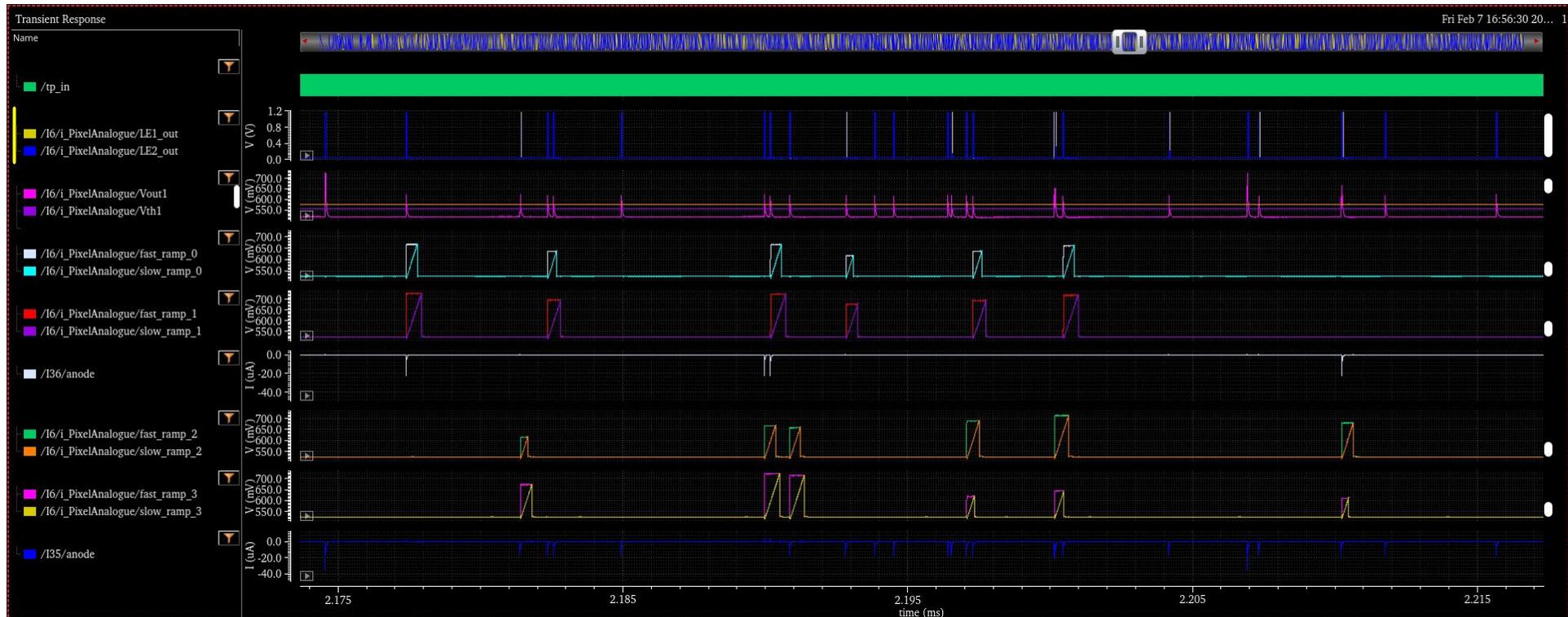
Good events: 842

Missing events: 22

Efficiency: 97.45%



Shutter mixed-signal simulation (SlewRate mode)



Shutter efficiency vs DCR (mixed-signal sim)



- Shutter width = 2.5 ns
- Input rate = 20 kHz
- Sim time = 20 ms

Ongoing: digital simulations (with improved DCR and photons signals model) to verify shutter distribution for the whole ALCOR chip and provide better statistics

Total simulation time = 19989730.664 ns
 Total number of dark counts = 811
Dark count rate = 40.571 kHz

Dark counts cut by shutter: 650
 Dark counts passed through shutter: 161
Shutter cut: 80.15%

Good events: 409
 Missing events: 1
Efficiency: 99.76%

Total simulation time = 19962950.756 ns
 Total number of dark counts = 1604
Dark count rate = 80.349 kHz

Dark counts cut by shutter: 1309
 Dark counts passed through shutter: 295
Shutter cut: 81.61%

Good events: 413
 Missing events: 3
Efficiency: 99.28%

Total simulation time = 19427451.802 ns
 Total number of dark counts = 3082
Dark count rate = 158.641 kHz

Dark counts cut by shutter: 2546
 Dark counts passed through shutter: 536
Shutter cut: 82.61%

Good events: 388
 Missing events: 2
Efficiency: 99.49%

Total simulation time = 19996870.504 ns
 Total number of dark counts = 6325
Dark count rate = 316.299 kHz

Dark counts cut by shutter: 5286
 Dark counts passed through shutter: 1039
Shutter cut: 83.57%

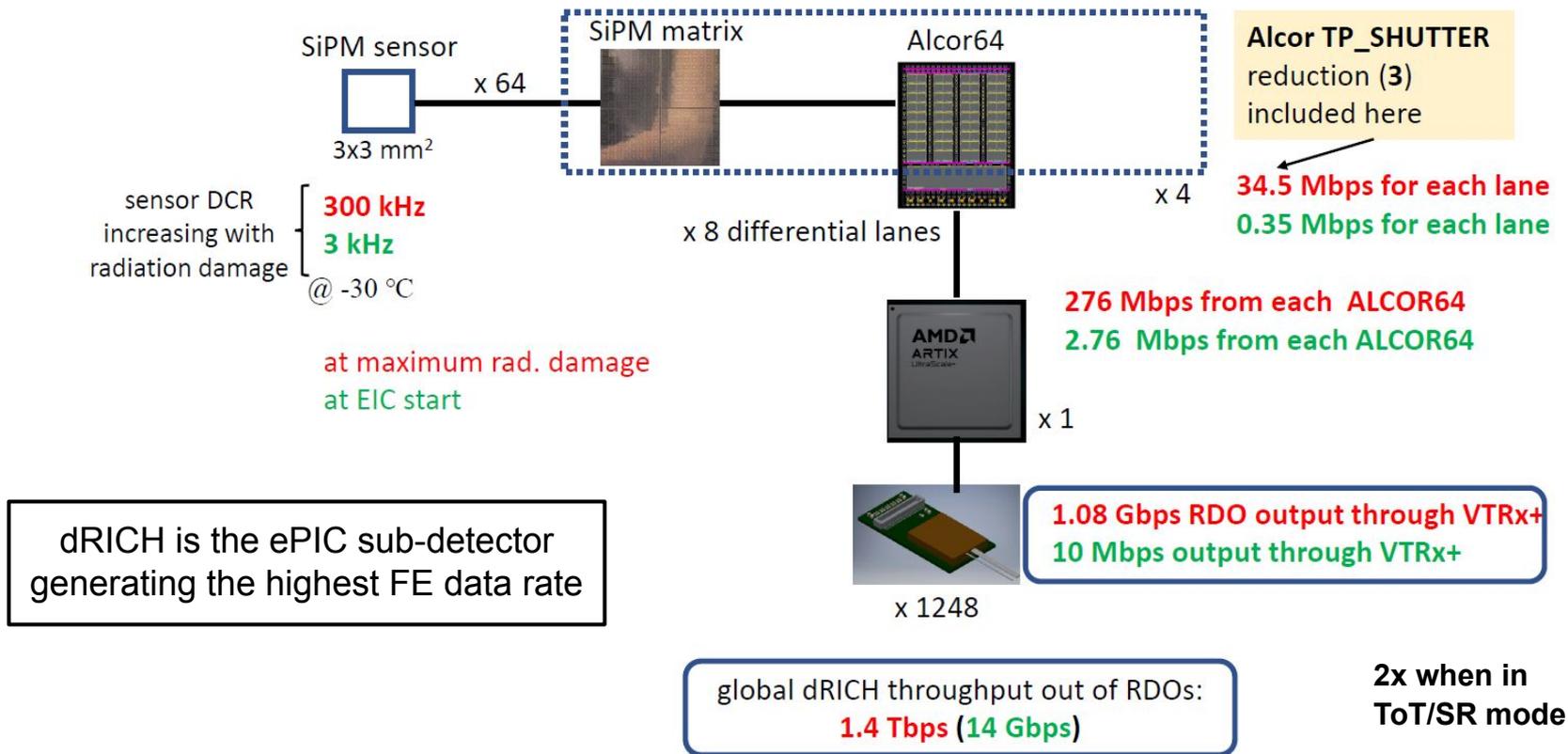
Good events: 412
 Missing events: 7
Efficiency: 98.33%

Total simulation time = 19532690.640 ns
 Total number of dark counts = 10006
Dark count rate = 512.269 kHz

Dark counts cut by shutter: 8411
 Dark counts passed through shutter: 1595
Shutter cut: 84.06%

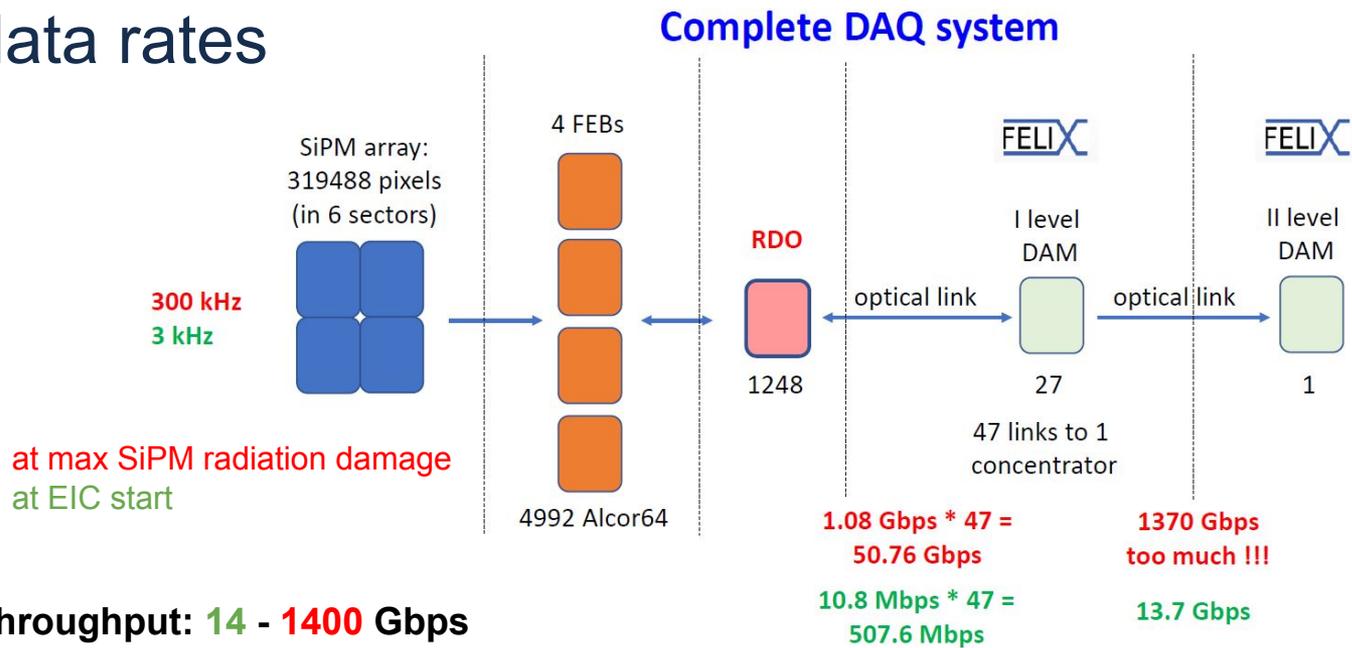
Good events: 842 (was 40 kHz)
 Missing events: 22
Efficiency: 97.45%

Data throughput from sensor to RDO optical link



The dRICH DAQ system has to be able to cope with such data rates: 14 Gbps \leftrightarrow 1.4 Tbps

dRICH data rates



Full detector throughput: 14 - 1400 Gbps

Possible problem of an excessive data bandwidth for the ePIC DAQ system when DCR = 300 kHz.

Two complementary approaches are being considered:

1. **dRICH interaction tagger** (INFN Genova): dedicated sub-detector (scintillating fibers + SiPM + ALCOR based readout) tagging relevant interactions
2. **ML online data filtering** (INFN Roma) at sub-detector level (Felix DAMs) against pure dark-count event

Power consumption

Estimated power consumption: **~12 mW/ch** → **< 1 W/chip**

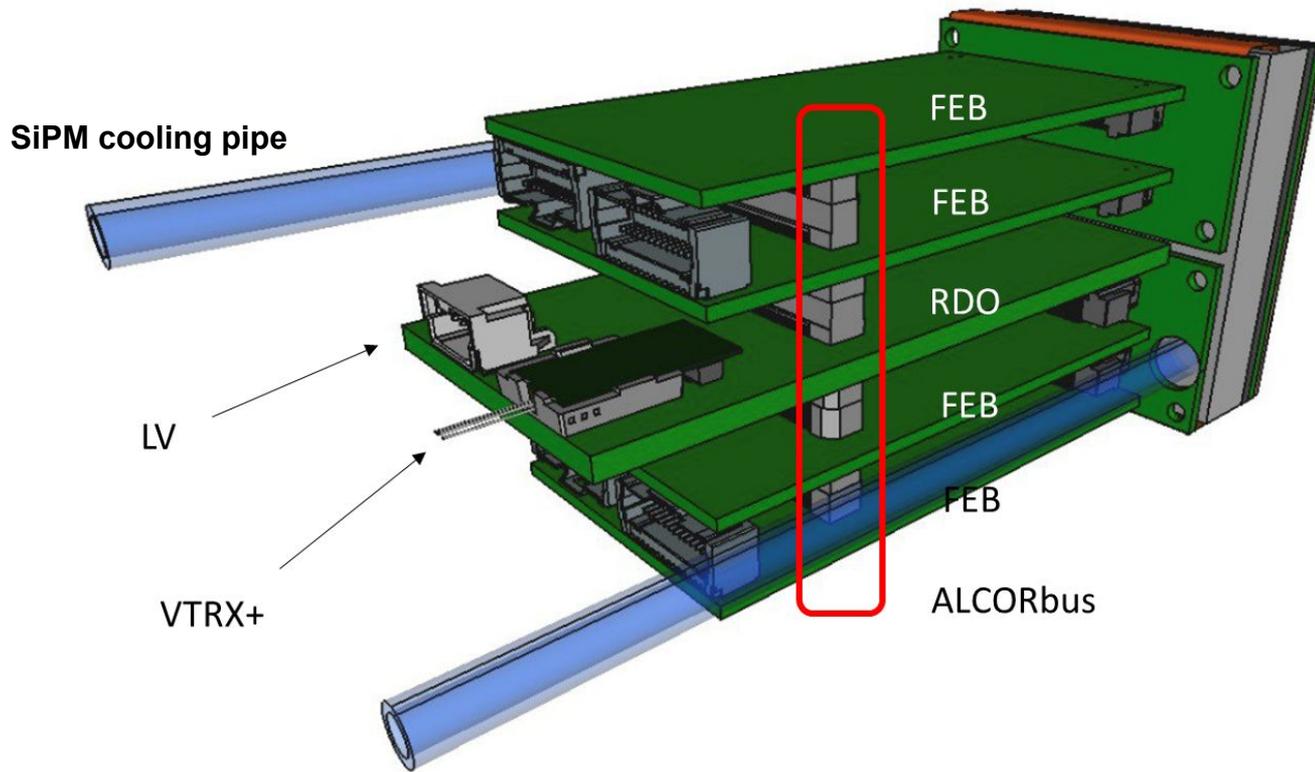
ALCOR requires 3 different power supplies

- **AVDD: 1.2 V** analogue core (<500 mA)
- **DVDD: 1.2 V** digital core (~275 mA)
- **DVDDIO: 2.5 V** digital IOs (~80 mA)

Generated on the FEB using LDO linear regulators ($V_{in} = 1.4 \text{ V}$ and 2.7 V)

- ✓ dRICH ALCOR **FEB design completed**: already including services for LV (analogue and digital VDD, linear regulators, current monitors, connectors towards off-detector power supply distribution boards), more details in next slides

dRICH photodetector unit (PDU)



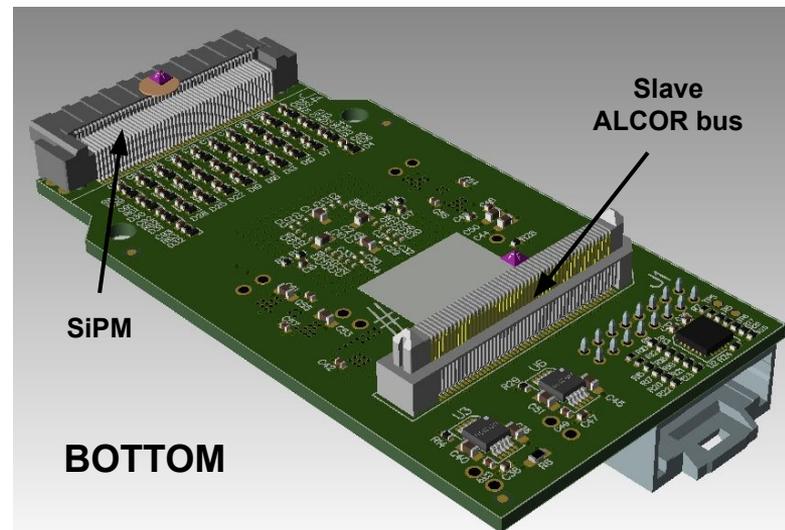
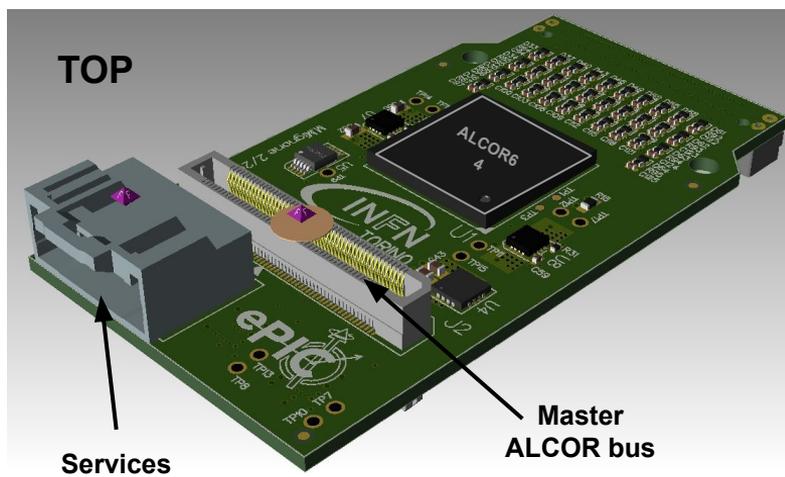
ALCOR FEB

Connectors:

- **Master ALCOR bus** (between RDO and 1st FEB, LVDS signals): *Samtec ERM5-050-04.0-L-DV-TR*
- **Slave ALCOR bus** (between 1st and 2nd FEB, LVDS signals): *Samtec ERF5-050-05.0-L-DV-K-TR*
- **Services connector** (SiPM $V_{\text{bias/annealing}}$, ALCOR LV, SiPM NTC sensor, 16 pins, max 2 A each): *Molex 2086591640*
- **SiPM connector** (SiPM signals, V_{bias} and $V_{\text{annealing}}$): *Samtec LSHM-150-01-L-RH-A-N-K-TR*

- **Dedicated PCB section for SiPMs HV routing**
- 2 $V_{\text{bias/annealing}}$ PCB layers/sections, each serving 32 SiPMs
 - **SiPM online annealing**: forward-bias, **I=60-100 mA** to reach **T=150°C** on SiPM matrix board
 - FEB to support **T up to 100°C**

- **Material: I-Tera MT40**
- **N layers: 10**



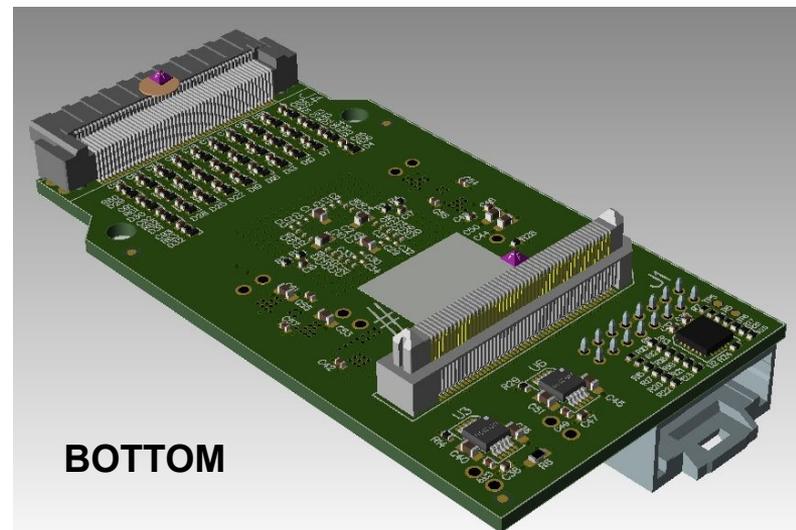
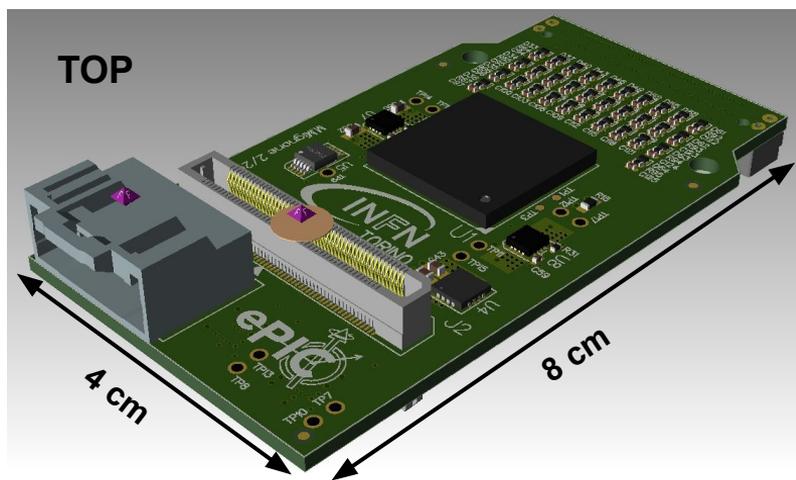
ALCOR FEB

Main components:

- **Linear Regulators** (2.5 V DVDD_IO, 1.2 V DVDD, 1.2 V AVDD): *Analog Devices ADP1752ACPZ-2.5-R7, ADP1761ACPZ-R7*
- **Current monitors** (before regulators): *Microchip Technology MIC2040-1YMM-TR*
- **I2C to Parallel-Port Expander** (RDO can read/control regulators and current monitors): *Texas Instruments PCF8575RGER*
- **RC high pass filter** (AC-coupling between SiPMs and ALCOR) + **annealing circuitry** (diodes)

Power segmentation:

- LV: 64 channels
- HV: 32 channels



Annealing + AC coupling circuit

AC coupling circuit

- cut SiPM signals tail
- protect ALCOR input from SiPM current during annealing

Annealing diode

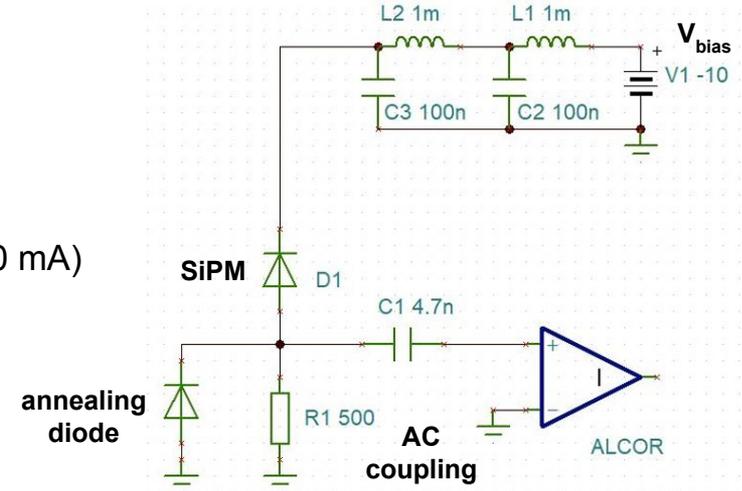
- provide path to ground for SiPM annealing current (up to 100 mA)
- trade-off between C_{in} and power

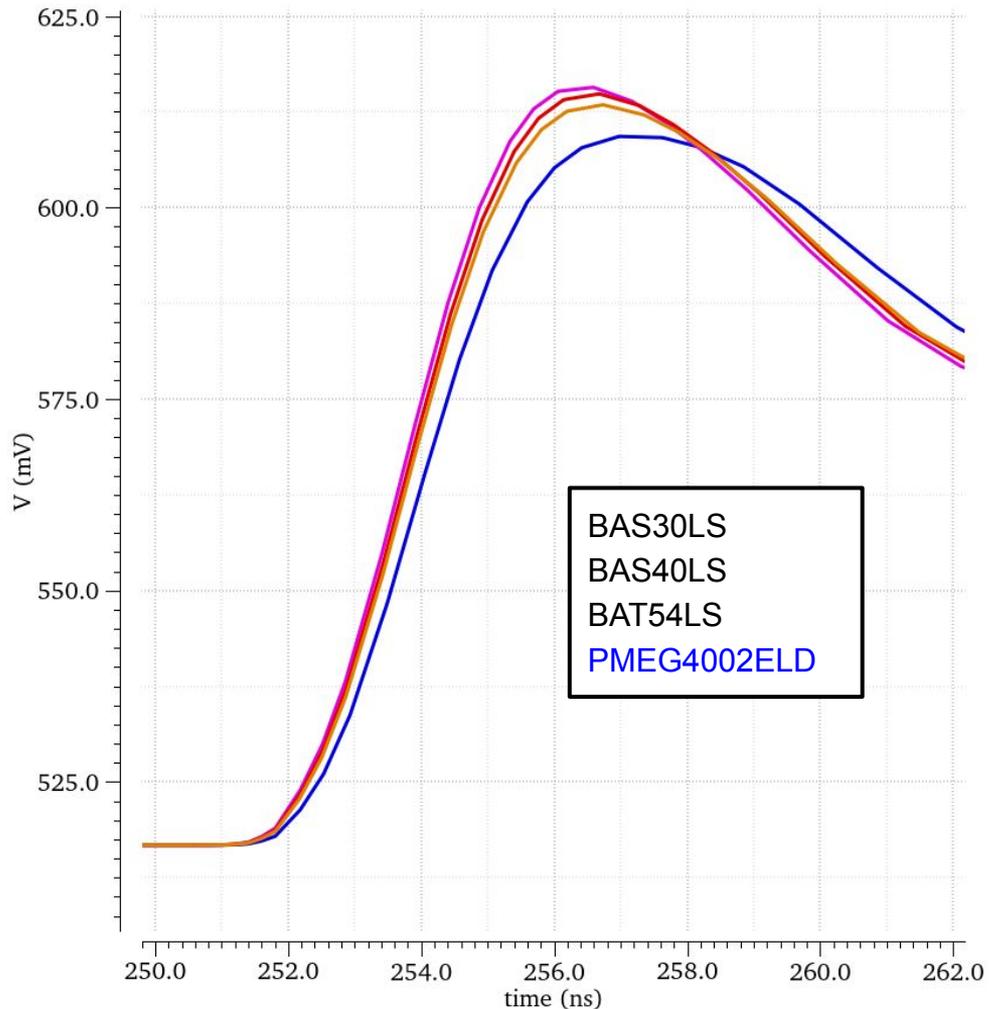
FEB prototype production

- select 2 different diodes but keep same footprint:
SMD0402, SOD882BD package

Annealing diodes survey:

- | | | | | | |
|----------------------|-------------------------------|------------------------|---|---------------------|-------------------------|
| • BAS30LS | $C = 2 \text{ pF}$ | $V_f = 0.85 \text{ V}$ | → | $P = 51 \text{ mW}$ | $(I_f = 60 \text{ mA})$ |
| • BAS40LS | $C = 5 \text{ pF}$ | $V_f = 0.68 \text{ V}$ | → | $P = 41 \text{ mW}$ | $(I_f = 60 \text{ mA})$ |
| • BAT54LS | $C = 10 \text{ pF}$ | $V_f = 0.48 \text{ V}$ | → | $P = 29 \text{ mW}$ | $(I_f = 60 \text{ mA})$ |
| • PMEG4002ELD | $C = 14\text{-}20 \text{ pF}$ | $V_f = 0.30 \text{ V}$ | → | $P = 18 \text{ mW}$ | $(I_f = 60 \text{ mA})$ |





ALCOR + ann. diodes simulations

Test input line capacitive loading due to diode capacitance

Larger C diode slightly reduces signal slope and thus time resolution (<10%)

Proposal for FEB prototypes (master + slave):

- 3+3 FEBs with **PMEG4002ELD**
- 3+3 FEBs with BAT54LS
- 1+1 FEBs without diodes

Thermal simulations (preliminary)

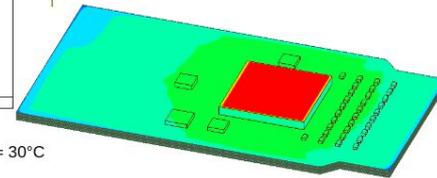
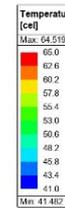


Preliminary thermal simulations of one FEB board during **normal operations** and while performing **annealing** embedded in a static $T = 30^{\circ}\text{C}$ ambient

Note: this is a first and simplified simulation of the board without air circulation and without taking into account other heat sources and the complexity of the surrounding environment

- first guidance on the possible **temperature profiles**
- useful to put **requirements** on **dRICH box cooling**
- valuable to **compare** with simplified **test benches**

Normal mode (ALCOR ON)



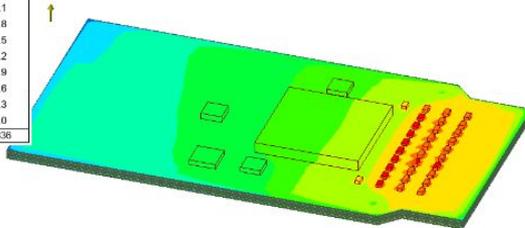
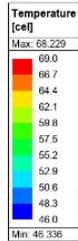
-Preg + Pbuffer
-Palc64 = 965mW

-BGA
 $T_j = 64.8^{\circ}\text{C}$

-PCB(Top):
 $T_{\text{max}} = 53^{\circ}\text{C}$
 $T_{\text{mean}} = 50^{\circ}\text{C}$

-PCB(Bot):
 $T_{\text{max}} = 52.7^{\circ}\text{C}$
 $T_{\text{mean}} = 50^{\circ}\text{C}$

Annealing mode ($V_f = 0.43\text{ V @ }70^{\circ}\text{C} \times 60\text{ mA} \rightarrow 26\text{ mW}$)



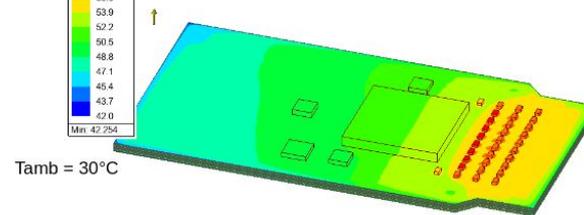
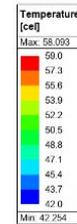
-DIODI:
64 x 26 mW
 $T_{\text{max}} = 68^{\circ}\text{C}$

-BGA:
 $T_{\text{max}} = 61^{\circ}\text{C}$
 $T_{\text{mean}} = 59^{\circ}\text{C}$

-PCB(Top):
 $T_{\text{max}} = 67^{\circ}\text{C}$
 $T_{\text{mean}} = 57^{\circ}\text{C}$

-PCB(Bot):
 $T_{\text{max}} = 68^{\circ}\text{C}$
 $T_{\text{mean}} = 57^{\circ}\text{C}$

Annealing mode ($V_f = 0.30\text{ V @ }55^{\circ}\text{C} \times 60\text{ mA} \rightarrow 18\text{ mW}$)



-DIODI:
64 x 18 mW
 $T_{\text{max}} = 58^{\circ}\text{C}$

-BGA:
 $T_{\text{max}} = 53^{\circ}\text{C}$
 $T_{\text{mean}} = 52^{\circ}\text{C}$

-PCB(Top):
 $T_{\text{max}} = 58^{\circ}\text{C}$
 $T_{\text{mean}} = 51^{\circ}\text{C}$

-PCB(Bot):
 $T_{\text{max}} = 58^{\circ}\text{C}$
 $T_{\text{mean}} = 51^{\circ}\text{C}$

SMA-annealing FEB

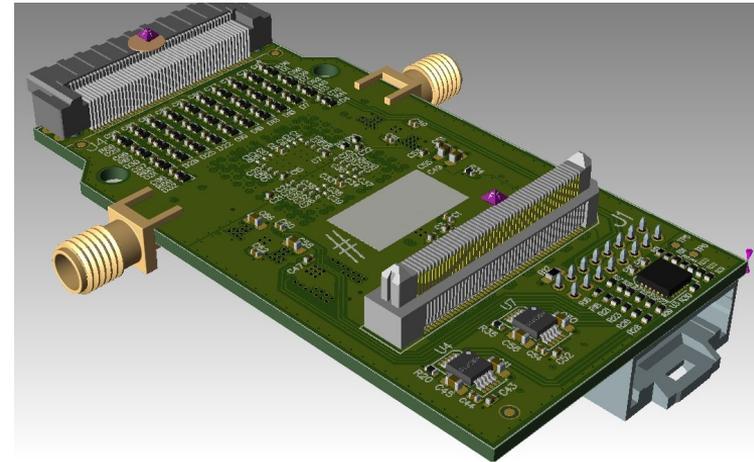
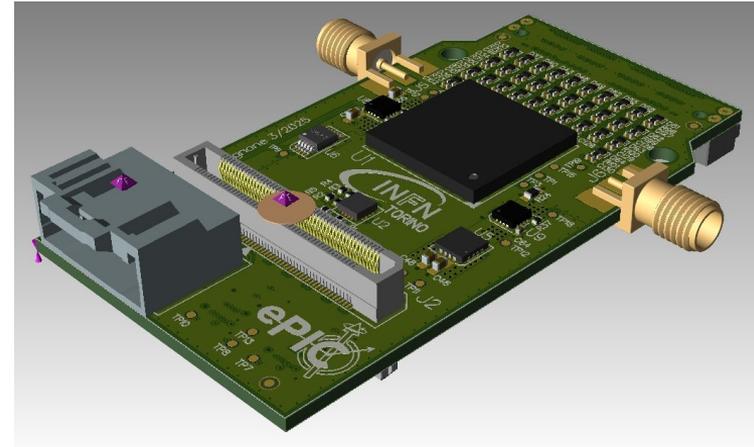
FEB prototype to test SiPM annealing

- like final FEB, with all annealing circuitry
- added **2 SMA connectors** to inspect SiPM signals (ALCOR inputs) on scope → initially can be used also without ALCOR-64

Goals:

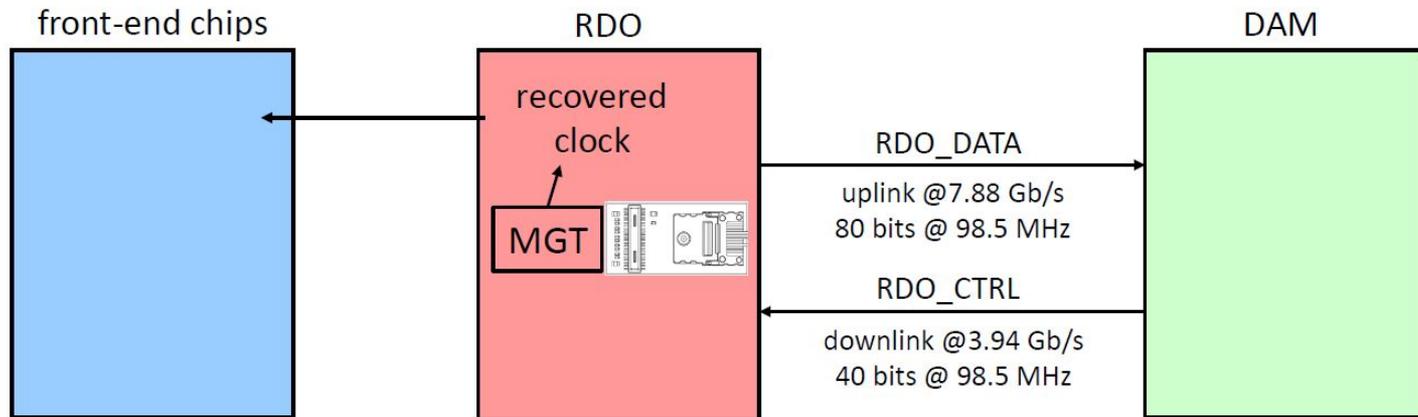
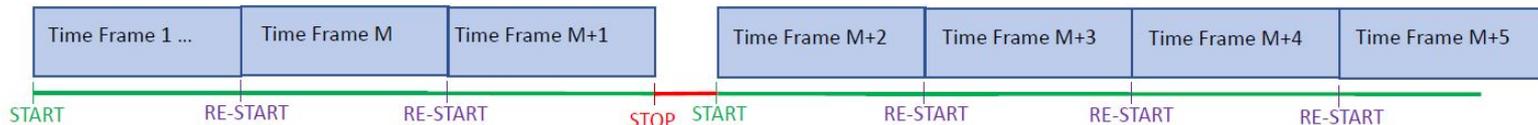
- test **realistic dRICH annealing electronics**
- study annealing process details and provide critical guidance for the final engineering and important reference data for **simulation of heat-dissipation** and the **design of the cooling system**

- ✓ **Purchase order issued 2-3 weeks ago**



Streaming readout

The ePIC detector will take data using a streaming data acquisition system with no traditional HW trigger



EIC clock = 98.5 MHz

BC = 10.15 ns

EIC orbit period = 12.7886 μ s = 1260 BCs

Time Frame = 2^{16} BCs = 0.66 ms

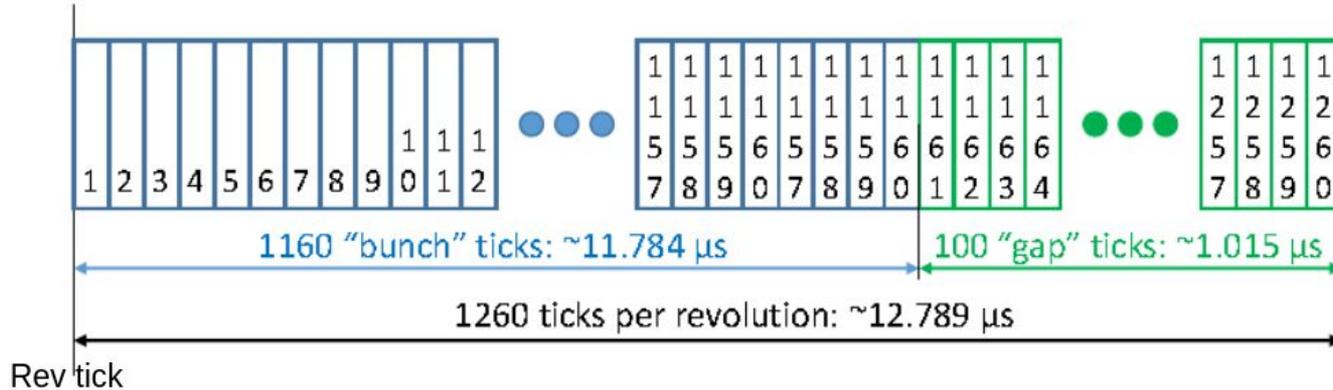
RDO_CTRL synchronous commands:

- SYNC_RESET: defines reference for time
- RUN_START: set internal state for readout
- RUN_RESTART: new time frame
- RUN_STOP: stop run

EIC beam structure and bunch crossing timing

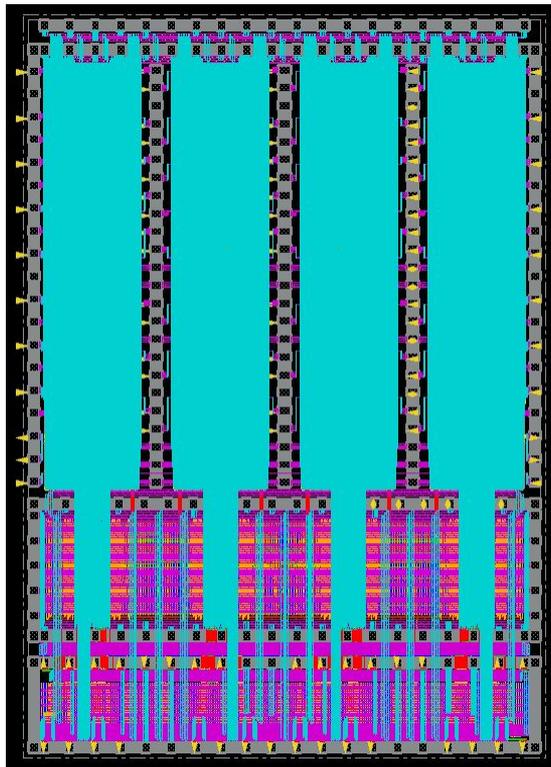


- Beam structure repeats every $\sim 12.7886 \mu\text{s}$
 - Revolution frequency: $\sim 78.195 \text{ kHz}$
- 1260 clock ticks in each revolution
 - Clock period: $\sim 10.14968 \text{ ns}$, frequency 98.52525 MHz → **ALCOR shutter frequency**
 - 1160 filled “bunch” ticks, may be not all filled with particles
 - 100 “gap” ticks without particles → **use for frame reset**

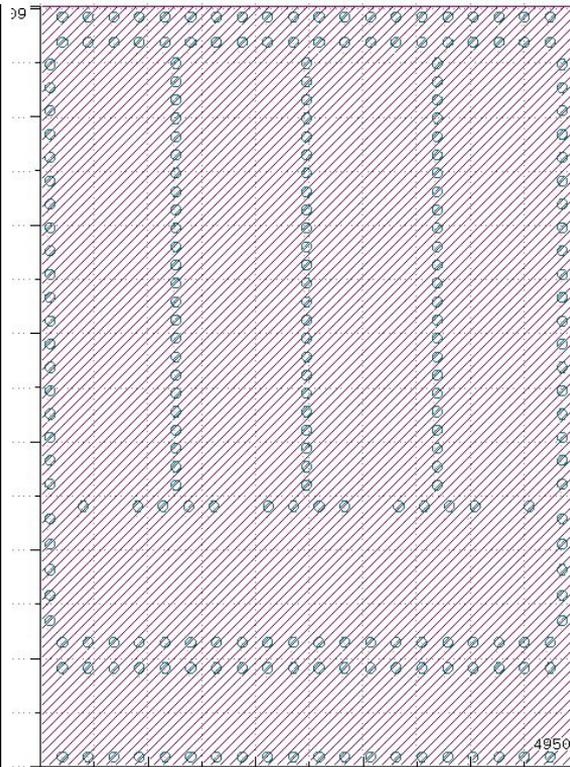


- ALCOR-64:
 - 7.02mm x 4.95mm
 - 234 PADs
- No dedicated redistribution layer (**RDL**) available in UMC 110nm technology
 - ASIC bump pads geometry not uniform
 - fan-out to BGA balls done on the interposer/substrate
- Bump pads pitch:
 - $\sim 170 \mu\text{m}$ (analog inputs)
 - $\sim 215 \mu\text{m}$

ALCOR-64 top layout



ALCOR-64 bump pads

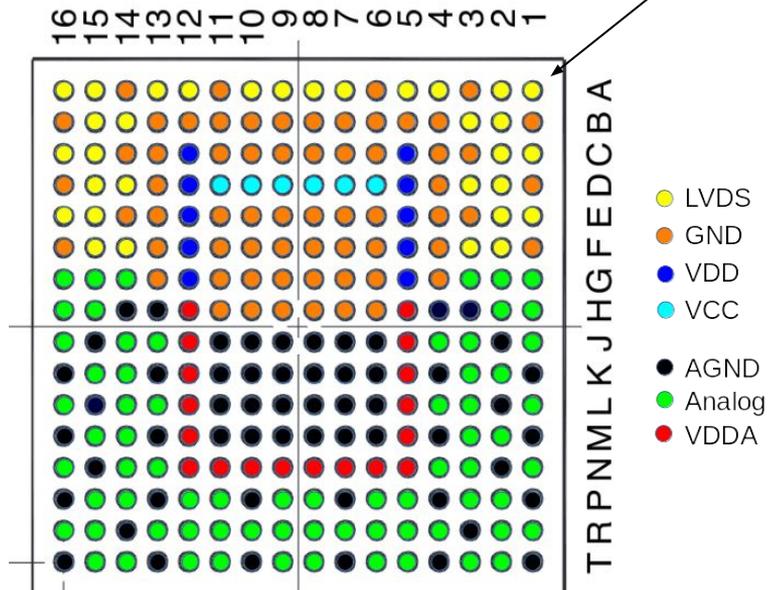
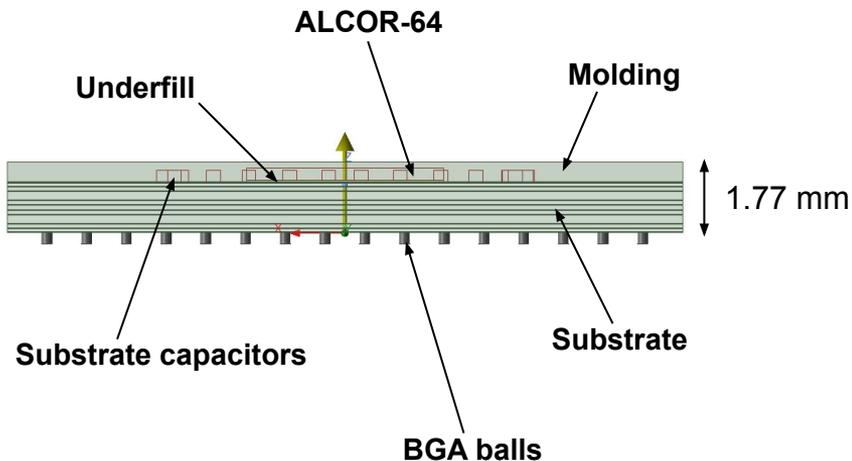
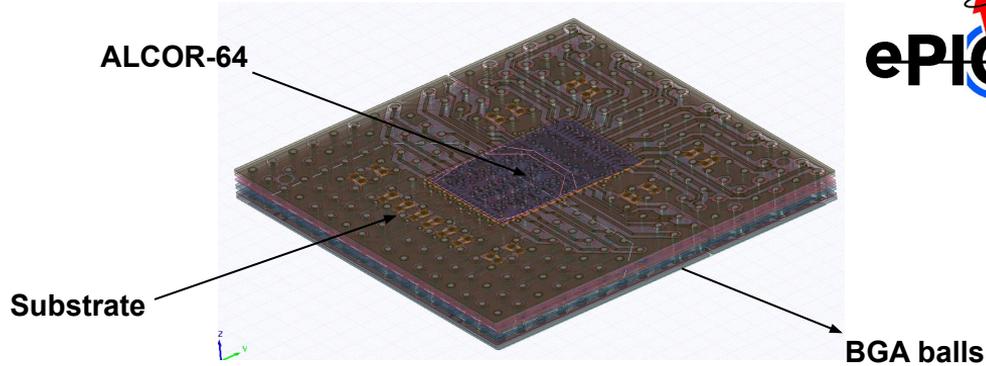


ALCOR BGA package

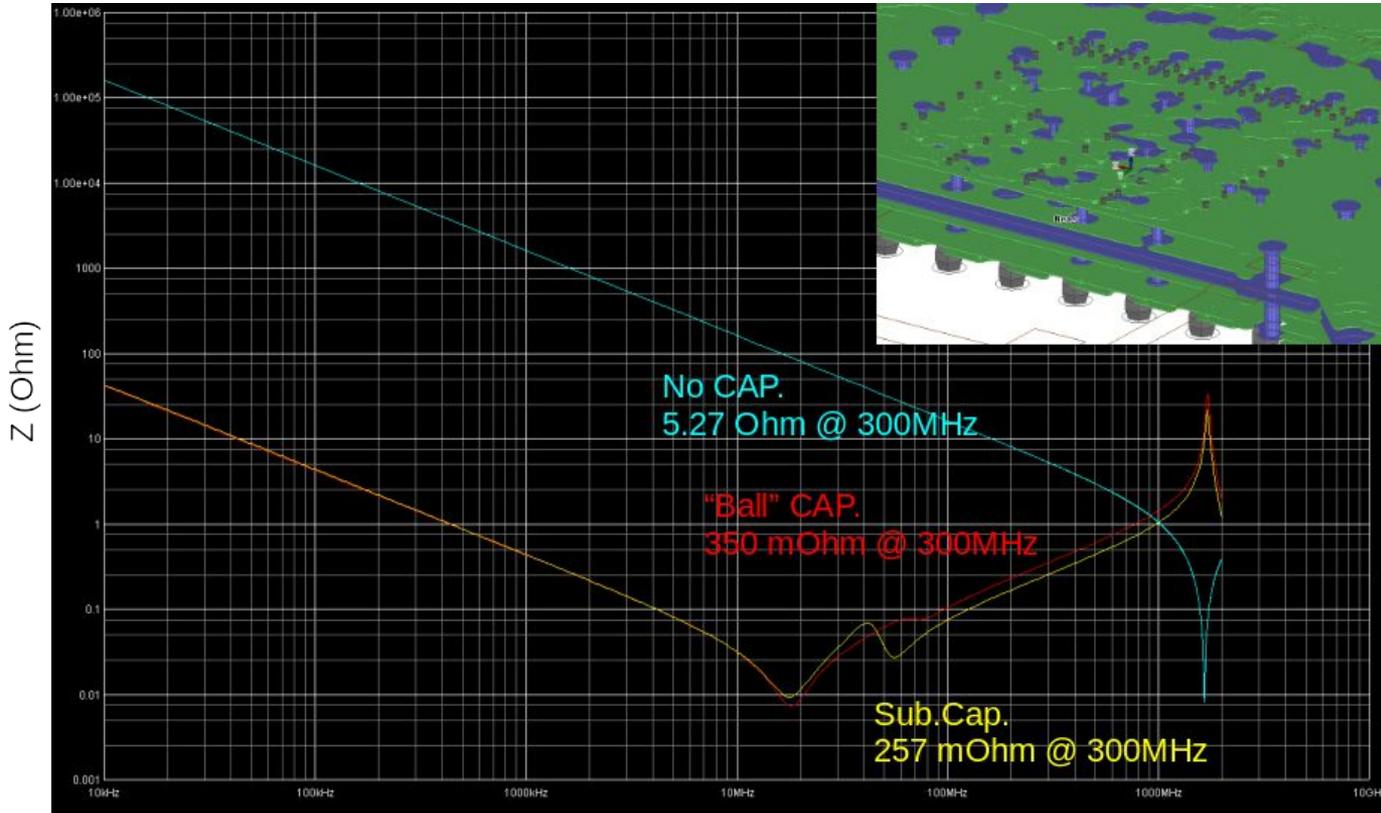


FC-BGA: flip-chip ball grid array

- BGA 256 (16 x 16)
- Size: 17 mm x 17 mm
- Ball pitch: 1 mm



ALCOR-64 substrate - simulations (Ball+PCB+Bump)



VDD-PDN (analog core supply power distribution network)

- **Sub.CAP:** substrate capacitors provides lower impedance
- **Ball CAP:** ideal case (not feasible)

Back-annotate this model into ALCOR simulations

ALCOR-64 substrate - simulations (Ball+PCB+Bump)



VDD-PDN (Digital core power supply)

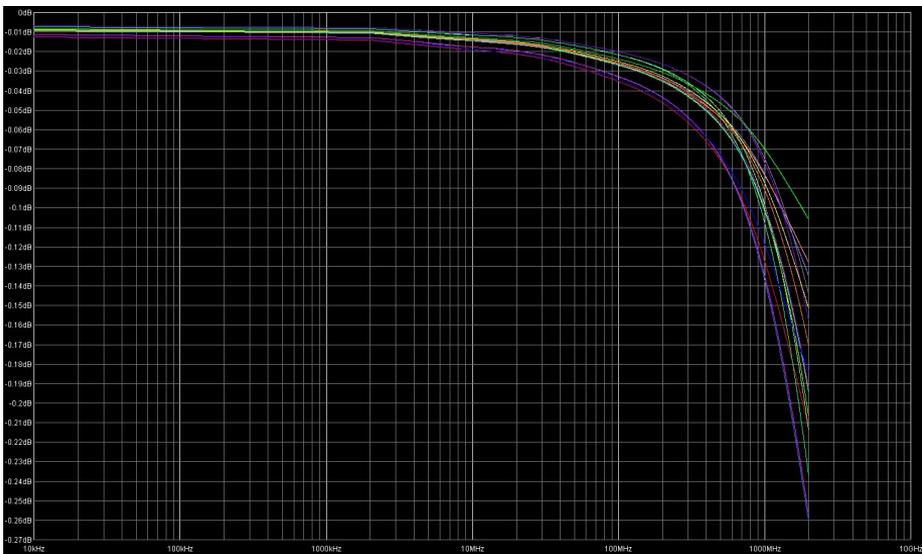


VCC-PDN (Digital IO power supply)

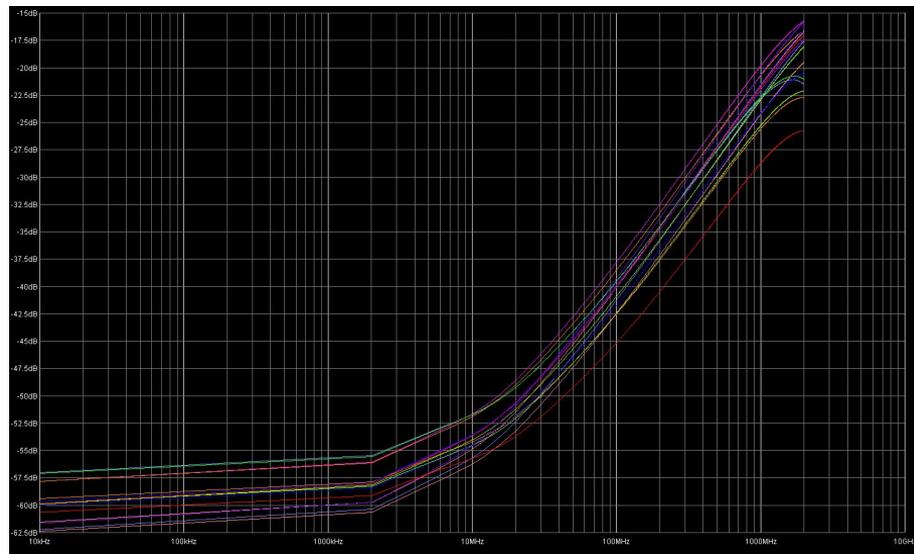
ALCOR-64 substrate - simulations (Ball+PCB+Bump)



Digital IO - LVDS transmission lines



Insertion loss: amount of energy that a signal loses as it travels along the PCB trace

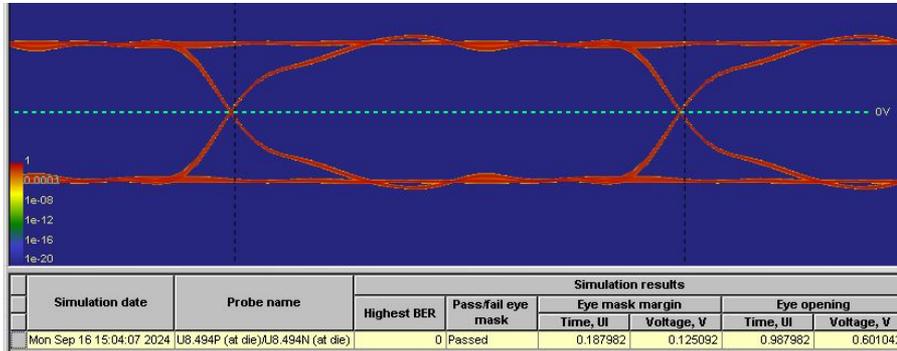


Return loss: loss of signal power due to signal reflection (impedance mismatch)

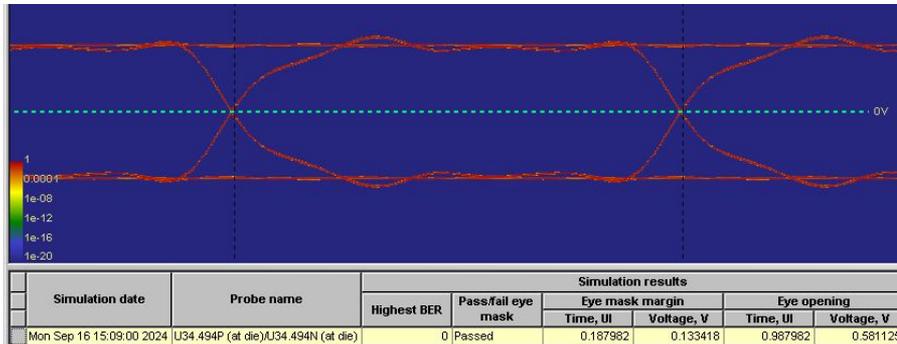
ALCOR-64 substrate - simulations (Ball+PCB+Bump)



Digital IO - LVDS transmission lines



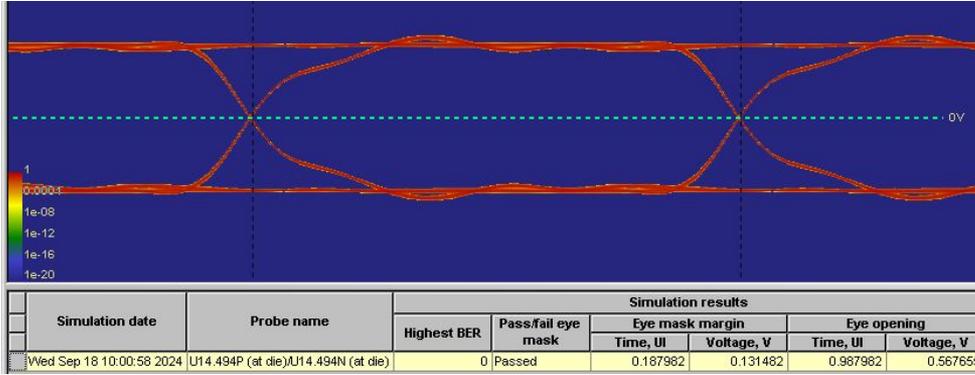
ALCOR substrate=Ball+Via+Line+Bump
Q0-PRBS 19bit 800Mbps



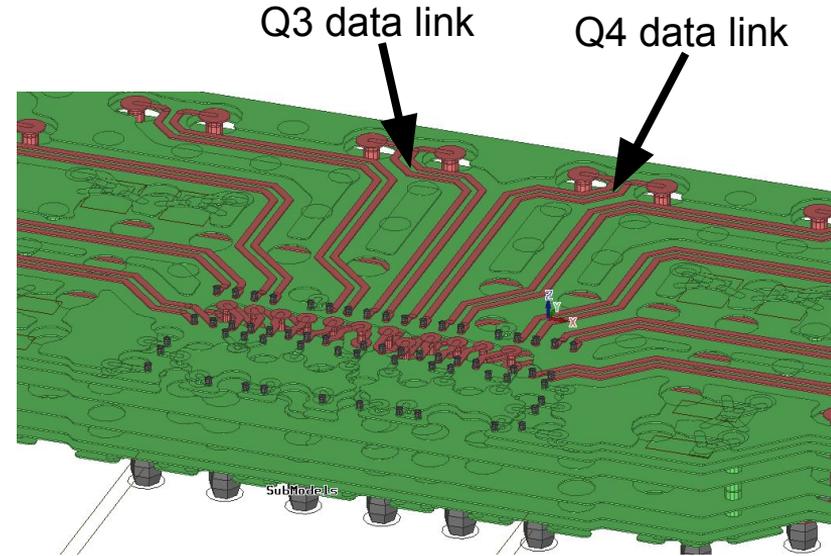
“Ideal” TLINE
Q0-PRBS 19bit 800Mbps

Tx and Rx model used is
LVDS_2V5 Driver (Artix UltraScale+)

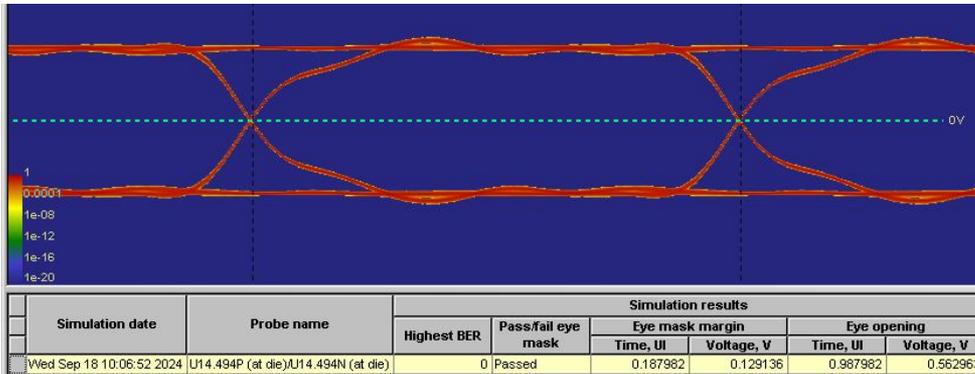
Q3-PRBS 19bit 800Mbps



Crosstalk



Q3-PRBS 19bit 800Mbps (+Q4 "Aggressor" Crosstalk PRBS 19bit 800 Mbps)

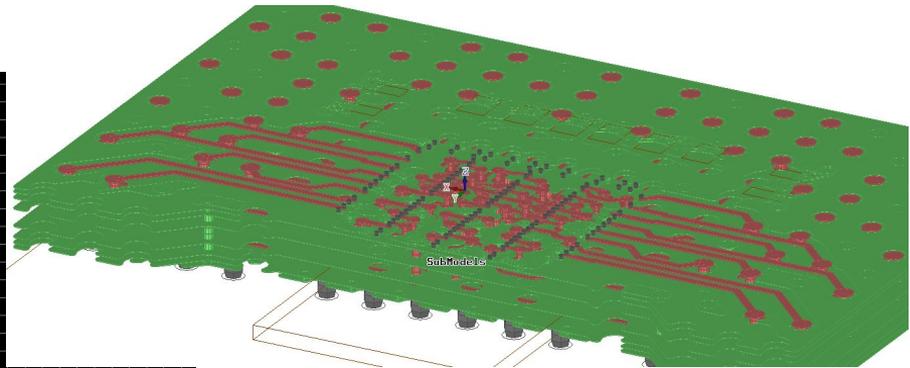
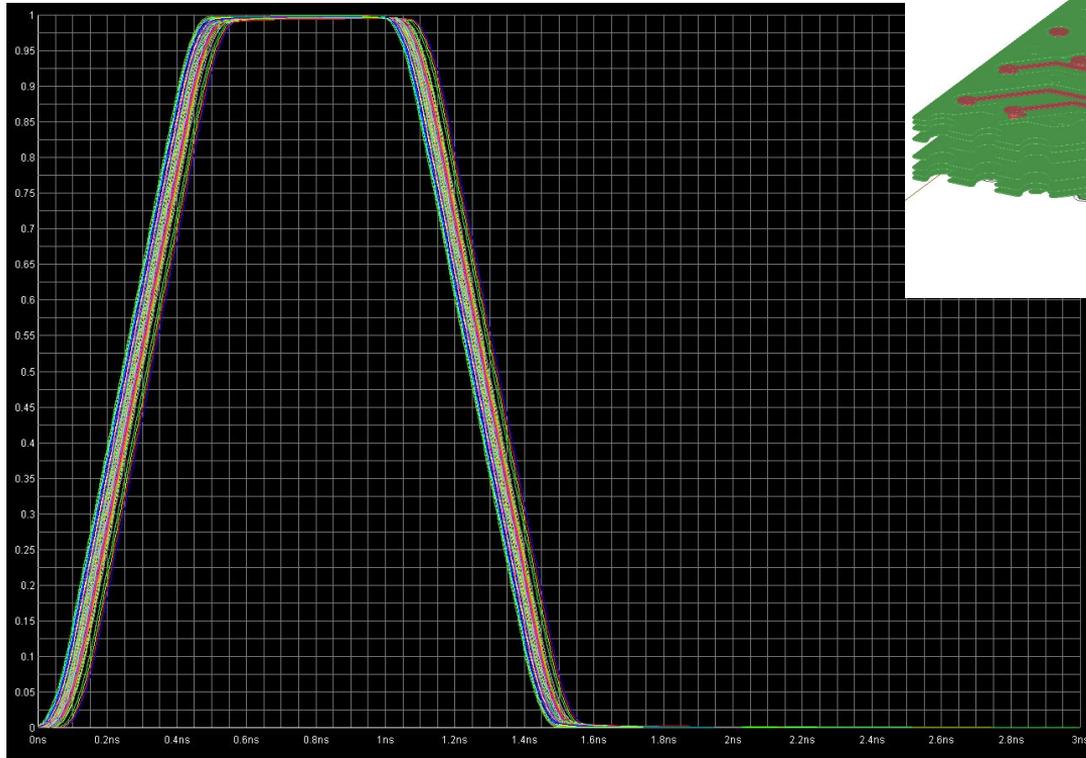


Tx and Rx model used is LVDS_2V5 Driver (Artix UltraScale+)

ALCOR-64 substrate - simulations (Ball+PCB+Bump)



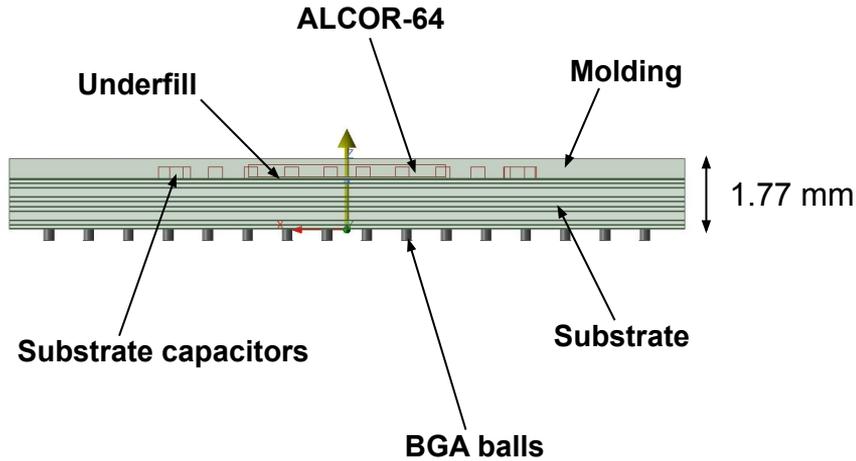
Analog inputs - 64 channels



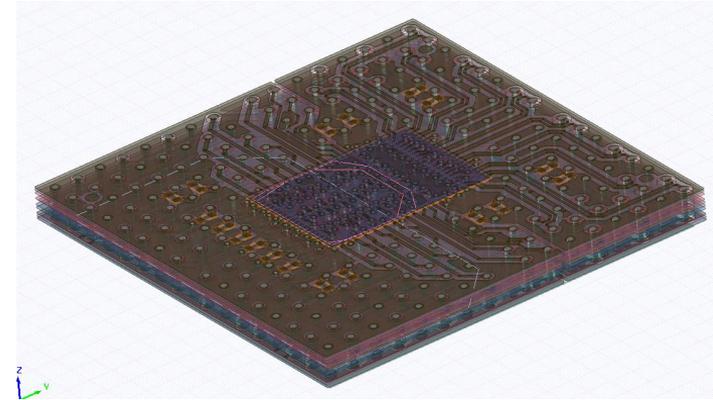
Input waveform:

- $T_p = 1 \text{ ns}$
- $T_r = 400 \text{ ps}$
- $T_f = 400 \text{ ps}$
- $Z_O = 50 \Omega$
- $Z_L = 50 \Omega$

Package Thermal Resistance



- Molding 0.5 mm (0.16 mm above ASIC)
- ALCOR-64
- Underfill
- Substrate



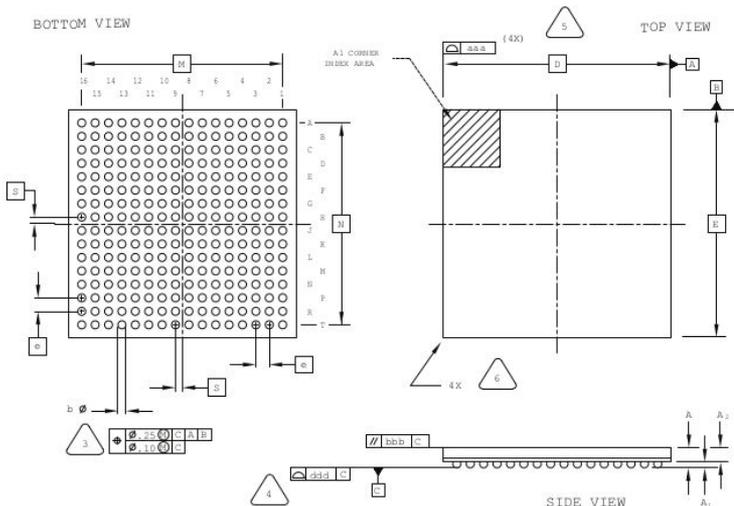
Package Thermal Resistance

- $\theta_{JB} \approx 12.9 \text{ }^\circ\text{C/W}$ (Junction-to-Board)
 - $\theta_{JC} \approx 3.3 \text{ }^\circ\text{C/W}$ (Junction-to-Case)
- } Good match with specs from commercial BGA datasheet

Commercial 256-ball BGA package datasheet

Table 2. Device/Package Thermal Resistance¹

Family	Device	Package	Dimensions	Pin Count	θ_{JA} (01fm) °C/W	θ_{JA} (200fm) °C/W	θ_{JA} (500fm) °C/W	θ_{JB} °C/W	θ_{JC} °C/W
LatticeECP2M™	LFE2M20E	FPBGA	17 x 17 mm	256	24.2	20.2	17.8	12.6	3.2
	LFE2M20E	FPBGA	23 x 23 mm	484	18.1	15.6	13.8	9.5	5.1
	LFE2M35E	FPBGA	17 x 17 mm	256	22.4	18.5	16.2	11.0	2.5
	LFE2M35E	FPBGA	23 x 23 mm	484	16.8	14.3	12.5	8.1	4.0
	LFE2M35E	FPBGA	27 x 27 mm	672	15.5	13.0	11.1	5.9	3.1
	LFE2M50E	FPBGA	23 x 23 mm	484	15.6	13.1	11.3	6.9	3.1
	LFE2M50E	FPBGA	27 x 27 mm	672	14.2	11.9	10.2	5.9	2.6
	LFE2M50E	FPBGA	31 x 31 mm	900	12.5	10.4	9.1	6.1	1.9
	LFE2M70E	FPBGA	31 x 31 mm	900	11.7	9.5	8.1	5.3	1.5
	LFE2M70E	FPBGA	35 x 35 mm	1152	13.7	12.0	11.0	6.5	2.0
	LFE2M100E	FPBGA	31 x 31 mm	900	10.8	8.6	7.7	4.5	1.2
	LFE2M100E	FPBGA	35 x 35 mm	1152	13.2	11.2	10.8	5.7	1.5
LatticeECP3™	LFE3-17	FTBGA	17 x 17 mm	256	24.5	20.6	18.2	12.9	3.3
	LFE3-17	CSBGA	10 x 10 mm	328	30.8	27.8	25.5	12.5	6.1
	LFE3-17	FPBGA	23 x 23 mm	484	18.4	15.8	14.1	9.8	5.4
	LFE3-35	FTBGA	17 x 17 mm	256	24.5	20.6	18.2	12.9	3.3
	LFE3-35	FPBGA	23 x 23 mm	484	18.4	15.8	14.1	9.8	5.4
	LFE3-35	FPBGA	27 x 27 mm	672	17.1	14.7	12.7	9.5	4.5
	LFE3-70	FPBGA	23 x 23 mm	484	15.7	13.2	11.4	7	3.2
	LFE3-70	FPBGA	27 x 27 mm	672	14.3	12	10.3	6	2.7
	LFE3-70	FPBGA	35 x 35 mm	1156	12.9	11.5	10.6	7.3	2.3



NOTES: UNLESS OTHERWISE SPECIFIED

1. DIMENSIONS AND TOLERANCES PER ANSI Y14.5M.

2. ALL DIMENSIONS ARE IN MILLIMETERS.

3. DIMENSION "b" IS MEASURED AT THE MAXIMUM SOLDER BALL DIAMETER, PARALLEL TO PRIMARY DATUM [C].

4. PRIMARY DATUM [C] AND SEATING PLANE ARE DEFINED BY THE SPHERICAL CROWNS OF THE SOLDER BALLS.

5. BILATERAL TOLERANCE ZONE IS APPLIED TO EACH SIDE OF THE PACKAGE BODY.

6. EXACT SHAPE AND SIZE OF THIS FEATURE IS OPTIONAL.

SYMBOL	MIN.	NOM.	MAX.
A	1.30	1.70	2.10
A1	0.30	0.50	0.70
A2	1.40 REF		
D/E	17.0 BSC		
M/N	15.0 BSC		
S	0.50 BSC		
b	0.50	0.60	0.70
e	1.0 BSC		
aaa	-	-	0.20
bbb	-	-	0.25
ddd	-	-	0.20

Geometry very similar to ALCOR BGA

Package Thermal Resistance

- $\theta_{JB} = 12.9$ °C/W (Junction-to-Board)
- $\theta_{JC} = 3.3$ °C/W (Junction-to-Case)

Results from our simulations match quite well specs from commercial BGA

Radiation tolerance

The dRICH-PDUs are in a moderately hostile radiation environment

- Φ (p+n > 20 MeV) = 200 Hz/cm²
 - TID \approx 2.3 krad (for 1000 fb⁻¹)
- } safety factor of 5 included

➤ Irradiation tests campaign: SEU/SEL and TID tests at Centro of Proton-Therapy in Trento with ALCOR-32 in Jul 2024 and Dec 2024

- Beam: 100 MeV proton
- Intensity: 10 - 100 nA
- Runs: typically 600 s
- Fluence collected per run: 10¹¹ - 10¹² p/cm²

- **Total fluence: 4.64 · 10¹² p/cm²** (Jul 2024) and **3.2 · 10¹² p/cm²** (Dec 2024)

- **Total TID: 436 krad**



Detailed results presented at the 29th Jan 2025 dRICH Meeting: <https://indico.bnl.gov/event/26313/>

SEU/SEL results (July 2024)



ECCR/BCR/PCR registers checked against SEU (every second)

- ECCR $\sigma = (9.4 \pm 1.8) \cdot 10^{-14} \text{ cm}^2/\text{bit}$ periphery register \rightarrow no TMR in ALCOR v2.1
- BCR $\sigma = (7.6 \pm 1.1) \cdot 10^{-14} \text{ cm}^2/\text{bit}$ periphery register \rightarrow no TMR in ALCOR v2.1
- **PCR** $\sigma = (3.3 \pm 0.5) \cdot 10^{-15} \text{ cm}^2/\text{bit}$ pixel register \rightarrow TMR (with auto-correction bug)

SEU rate in ePIC:

- dRICH Flux = $140 \text{ (h > 20 MeV) / (cm}^2 \text{ s)}$
- ALCOR bits: $(2048 + 192) = 2240 \rightarrow$ ALCOR-64 bits will be 4480
- Total ALCOR: 4992
- Total bits: $4992 \cdot 4480 = 2.2 \cdot 10^7 \text{ bits}$

*SEU due to accumulating bit flips
in triplicated registers over time*

- $\sigma = 3.3 \cdot 10^{-15} \text{ cm}^2/\text{bit} \rightarrow$ **MTBF** = $9.8 \cdot 10^4 \text{ seconds} \rightarrow$ every **27 hours**
- No latchup events (from power supply currents monitoring)

SEU rate is within the expected manageable levels

SEU/SEL results (December 2024)



ECCR/BCR/PCR registers checked against SEU (every second), **PCR re-written every 10 seconds to “mask” TMR auto-correction bug**

- ECCR $\sigma = 9.8 \cdot 10^{-14} \text{ cm}^2/\text{bit}$ periphery register → no TMR in ALCOR v2.1
- BCR $\sigma = 6.1 \cdot 10^{-14} \text{ cm}^2/\text{bit}$ periphery register → no TMR in ALCOR v2.1
- PCR **no SEU detected** re-written every 10 seconds to avoid TMR auto-correction bug

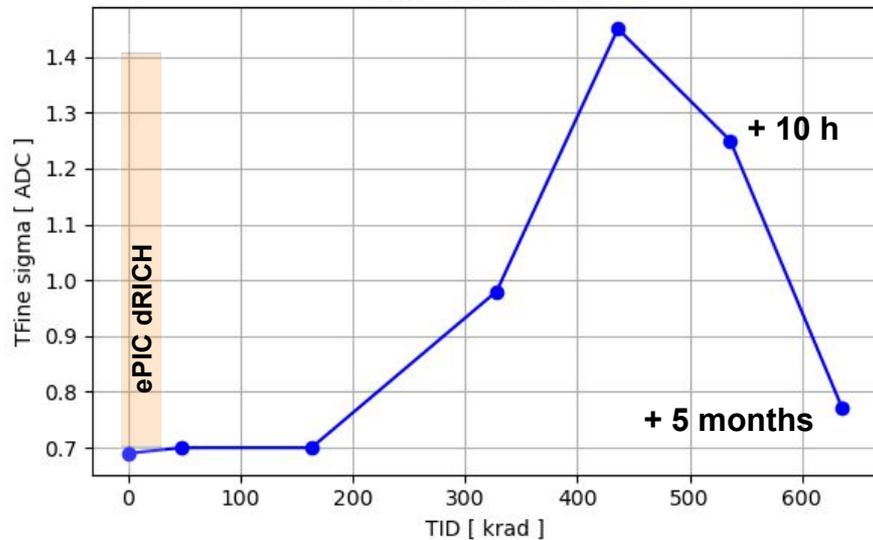
ALCOR v3: TMR SEU protection added also for periphery registers (used *CERN TMRG tool* for all registers), Hamming code SEU protection for FSMs

- All configuration registers: TMR with voting and self correction
- Pixel and EoC Readout FSMs: Hamming Code (Single Error Correction)
- EoC Reset FSM: TMR with voting and self correction
- SPI address counters: TMR with voting and self correction
- SPI shift register not protected

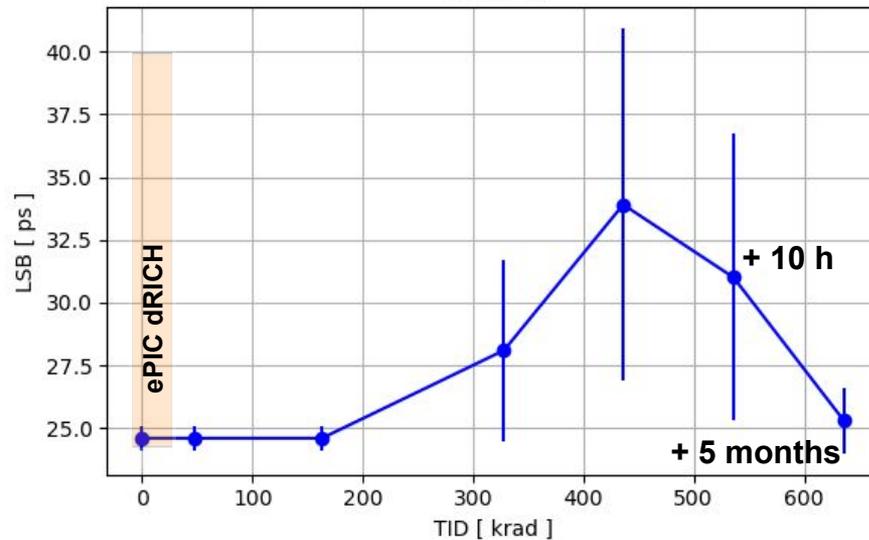
TID results - TDC error & LSB

*last two points = 436 krad after 10 hours and 5 months

TFine Sigma Mean



TDC LSB



- Technology is sufficiently radiation tolerant to be used in the ePIC dRICH environment
- Similar results w.r.t. irradiation tests performed on another ASIC with same technology [1]
- Also other FEB components will be tested and validated

[1] F. Lenta *et al* 2024 *JINST* **19** C04047,
DOI 10.1088/1748-0221/19/04/C04047